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Honda

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(54) **LIGHT-EMITTING DEVICE AND DRIVING METHOD THEREOF**

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(30) **Foreign Application Priority Data**

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H01L 27/12 (2006.01)

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(52) **U.S. Cl.**

CPC **H01L 27/1251** (2013.01); **G09G 3/3233** (2013.01); **G09G 2300/0439** (2013.01); **G09G 2300/0819** (2013.01); **G09G 2320/043** (2013.01); **G09G 2320/045** (2013.01)

USPC **345/76**; **345/214**

(58) **Field of Classification Search**

CPC G09G 3/30
See application file for complete search history.

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Primary Examiner — Andrew Sasinowski

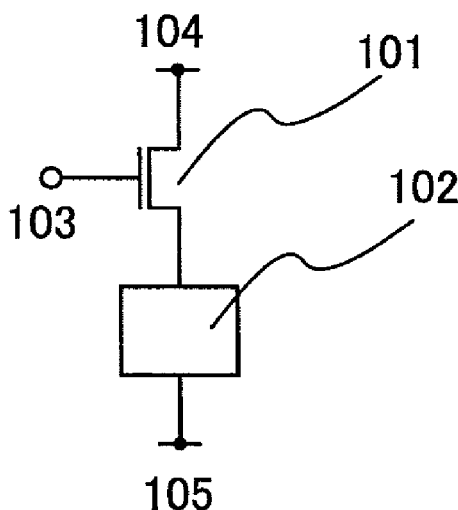
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(57)

ABSTRACT

Charge corresponding to a potential difference between electrodes of an electroluminescence element is accumulated in a period in which the electroluminescence element emits light; the potential difference is detected without decrease in the luminance at the time of light emission of the electroluminescence element; and a reference potential of one electrode of the electroluminescence element is changed based on the detected potential difference, so that reduction in luminance of the electroluminescence element due to deterioration of the electroluminescence element is compensated.

32 Claims, 17 Drawing Sheets



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FIG. 1

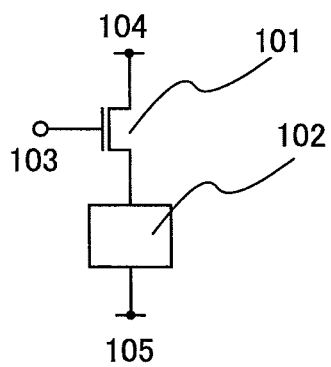


FIG. 2A

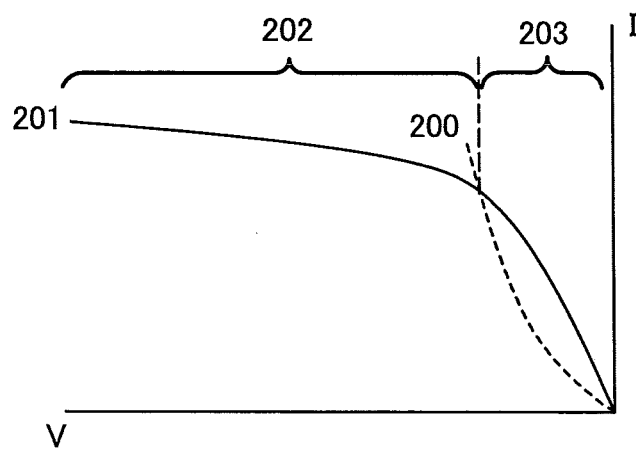


FIG. 2B

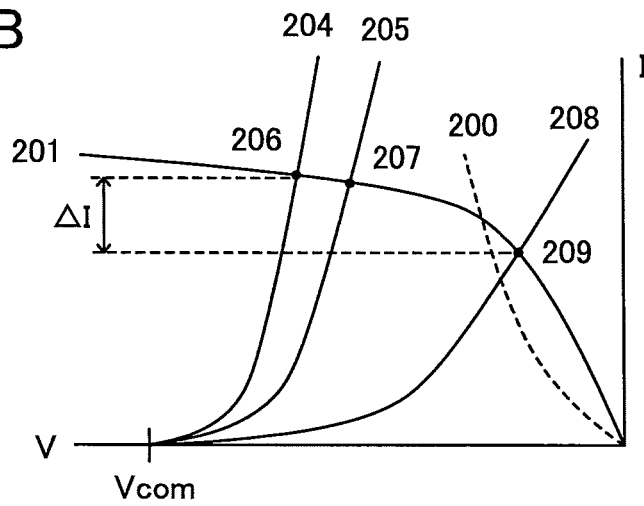


FIG. 3A

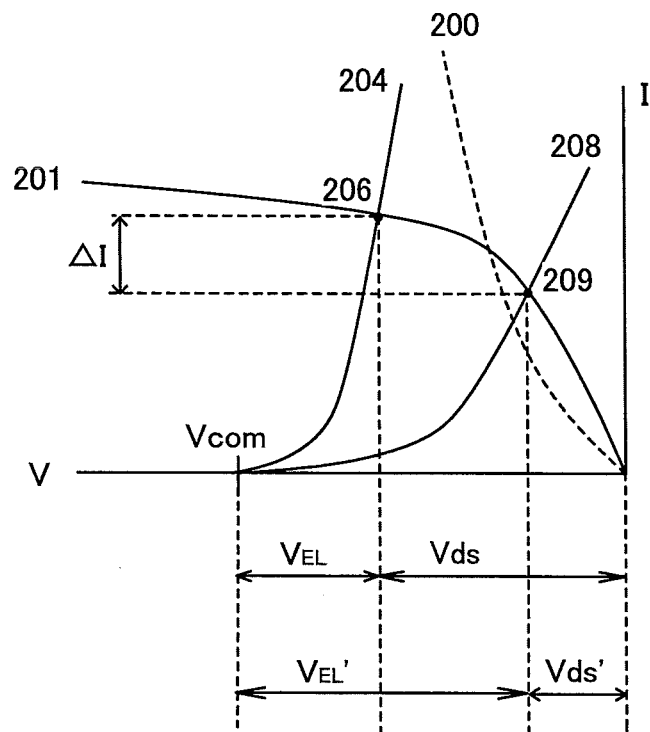


FIG. 3B

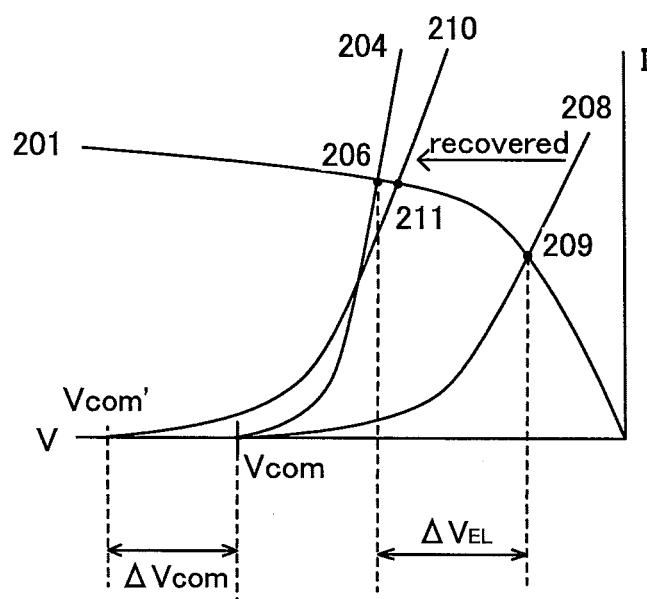


FIG. 4A

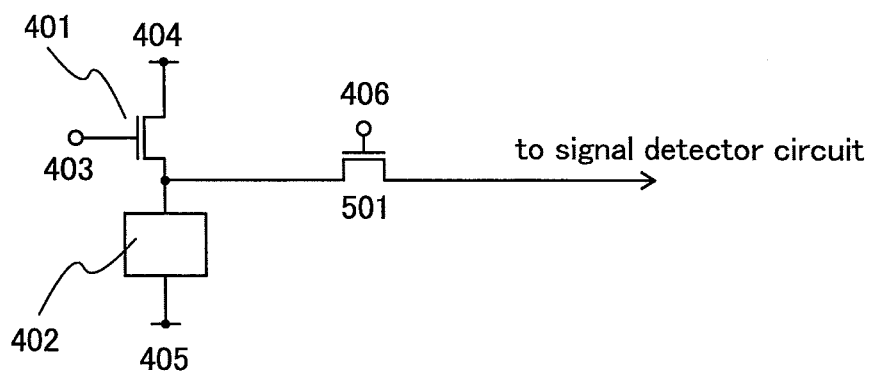


FIG. 4B

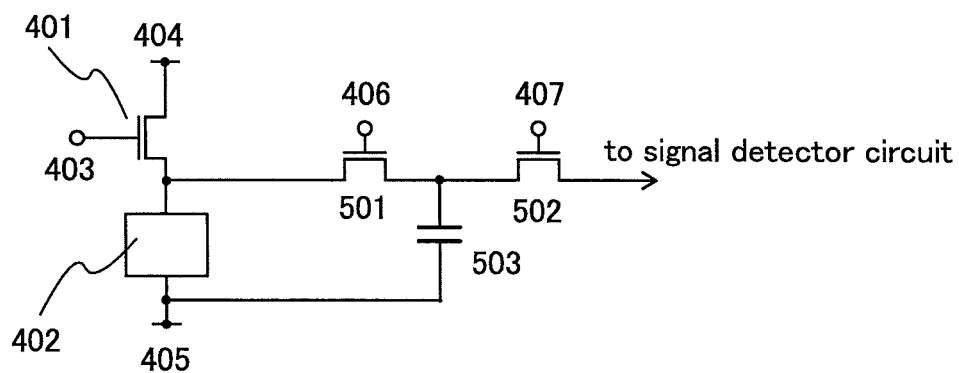


FIG. 5

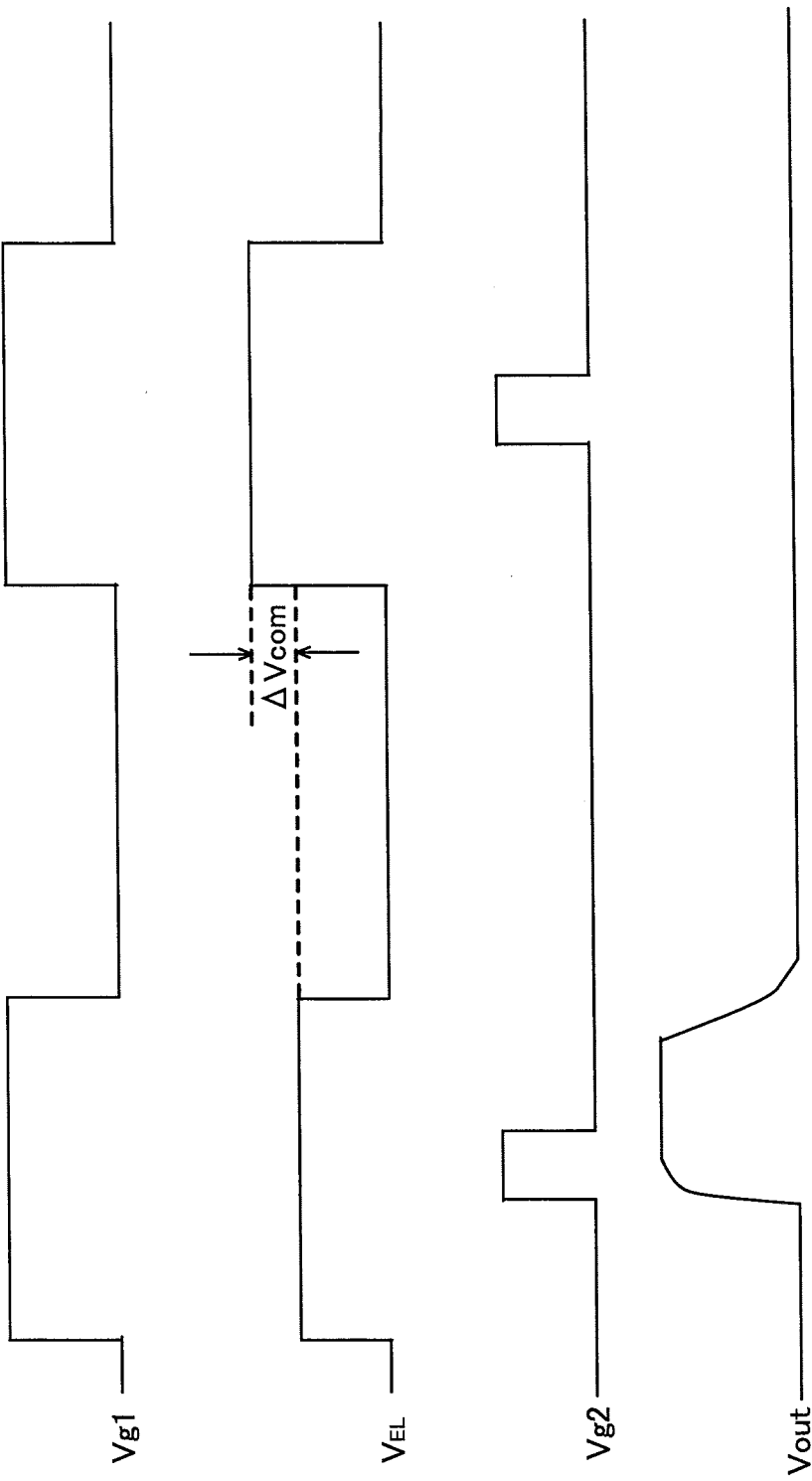


FIG. 6

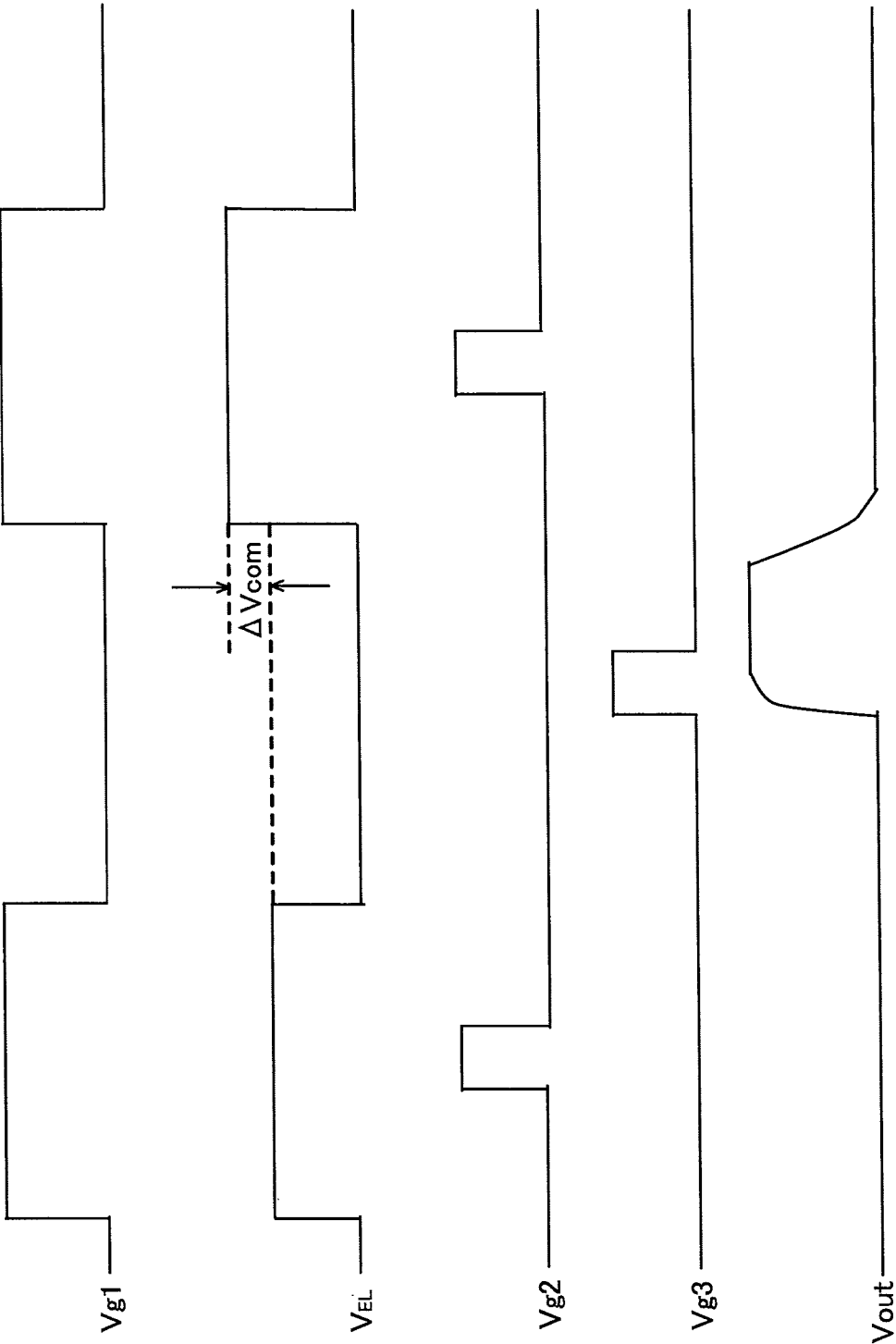


FIG. 7A

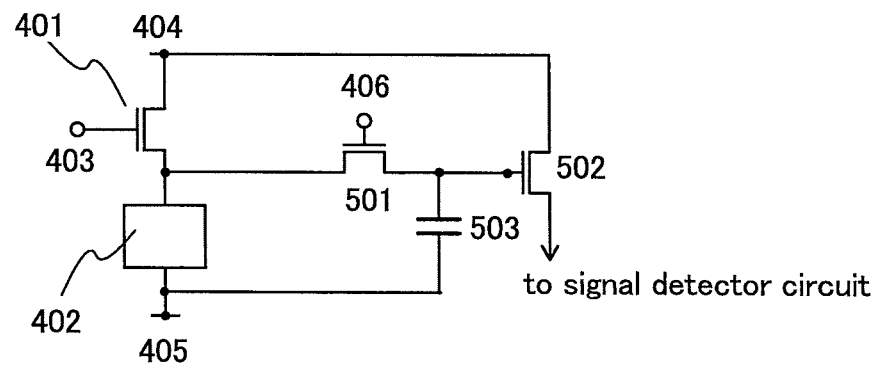


FIG. 7B

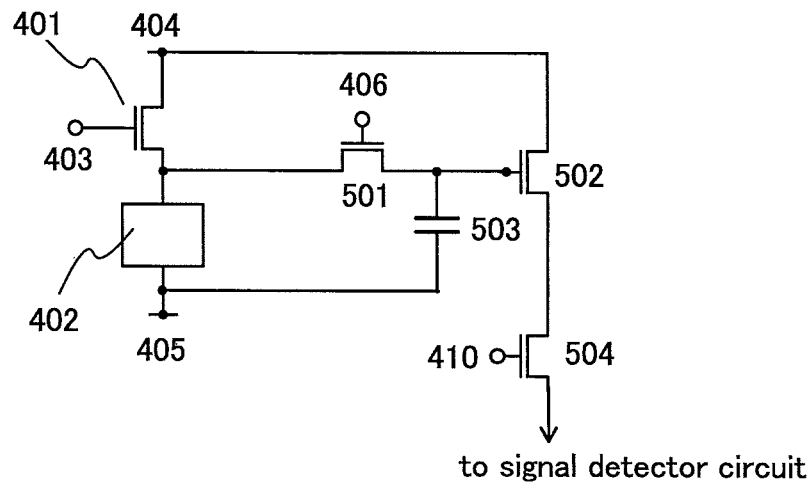


FIG. 8

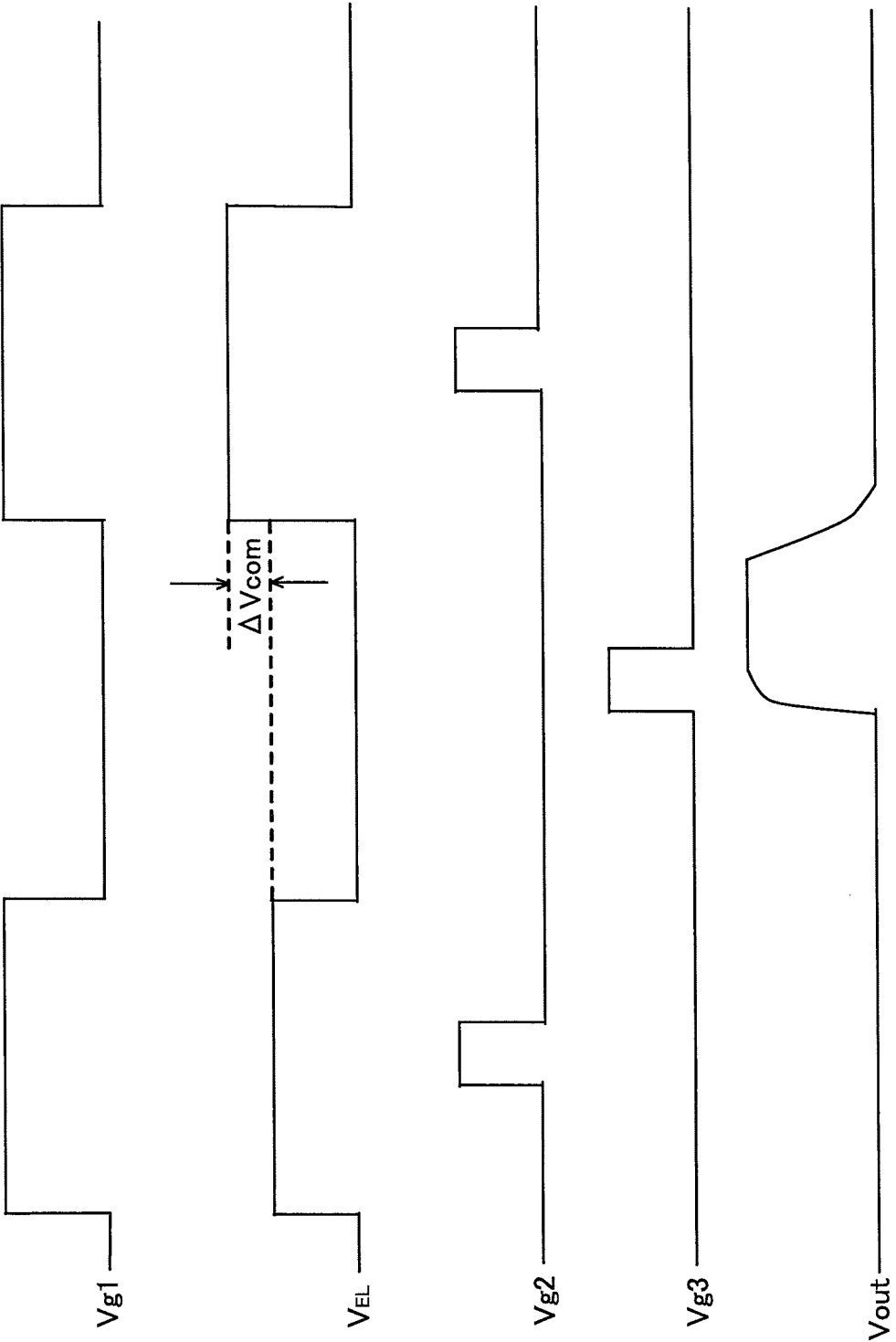


FIG. 9

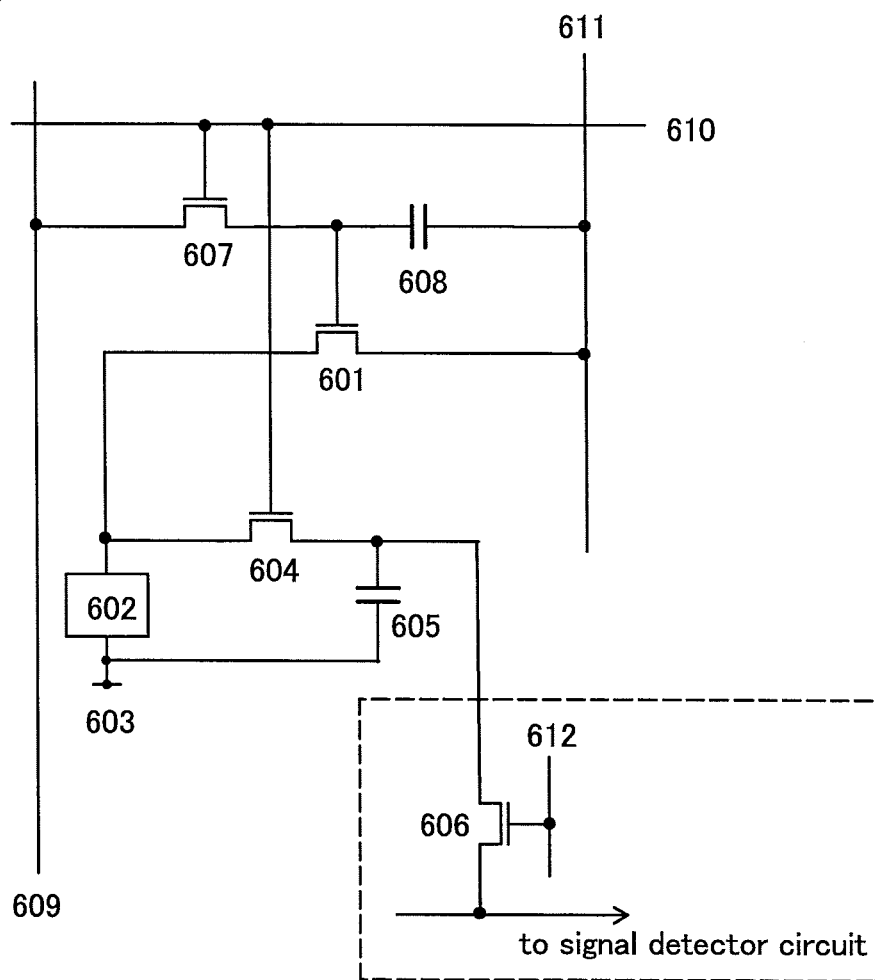


FIG. 10

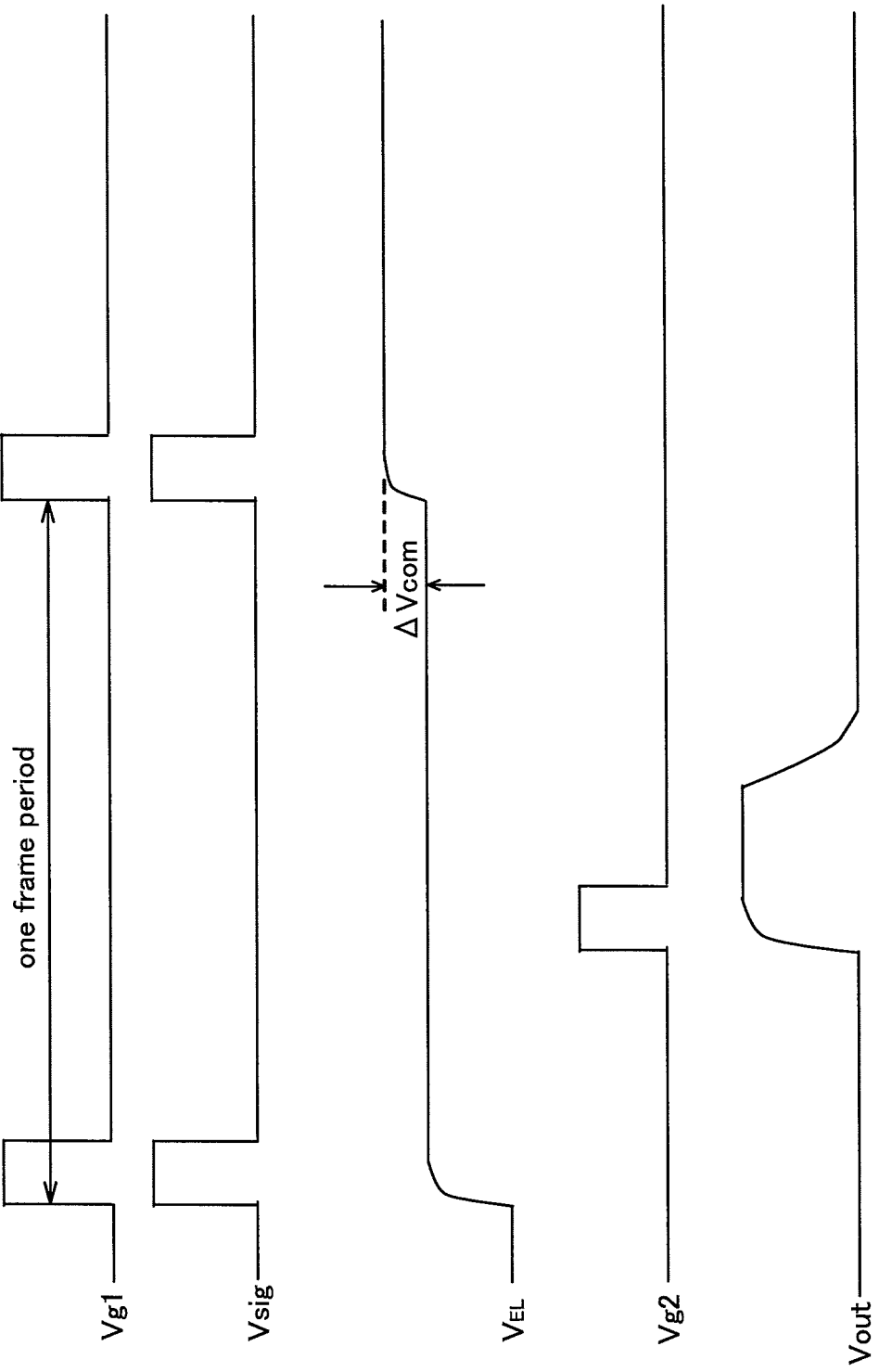


FIG. 11

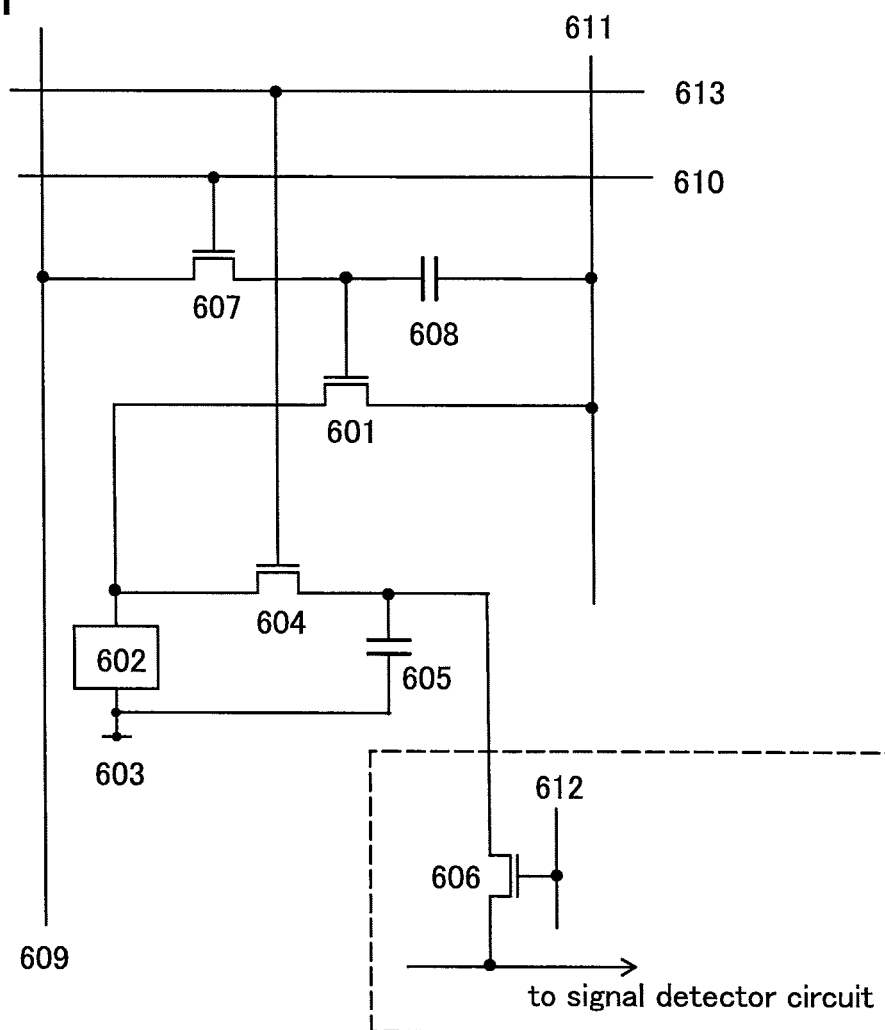


FIG. 12

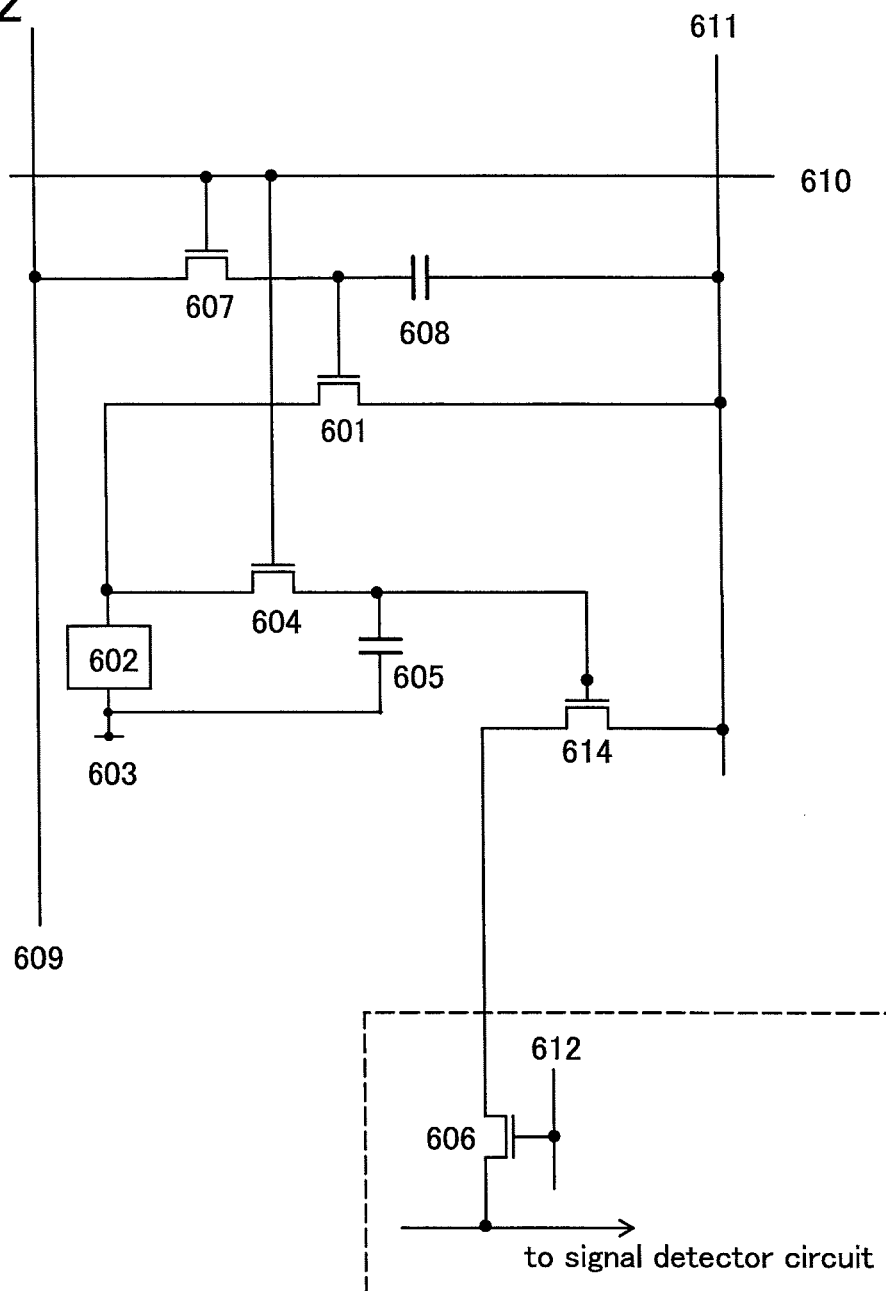


FIG. 13

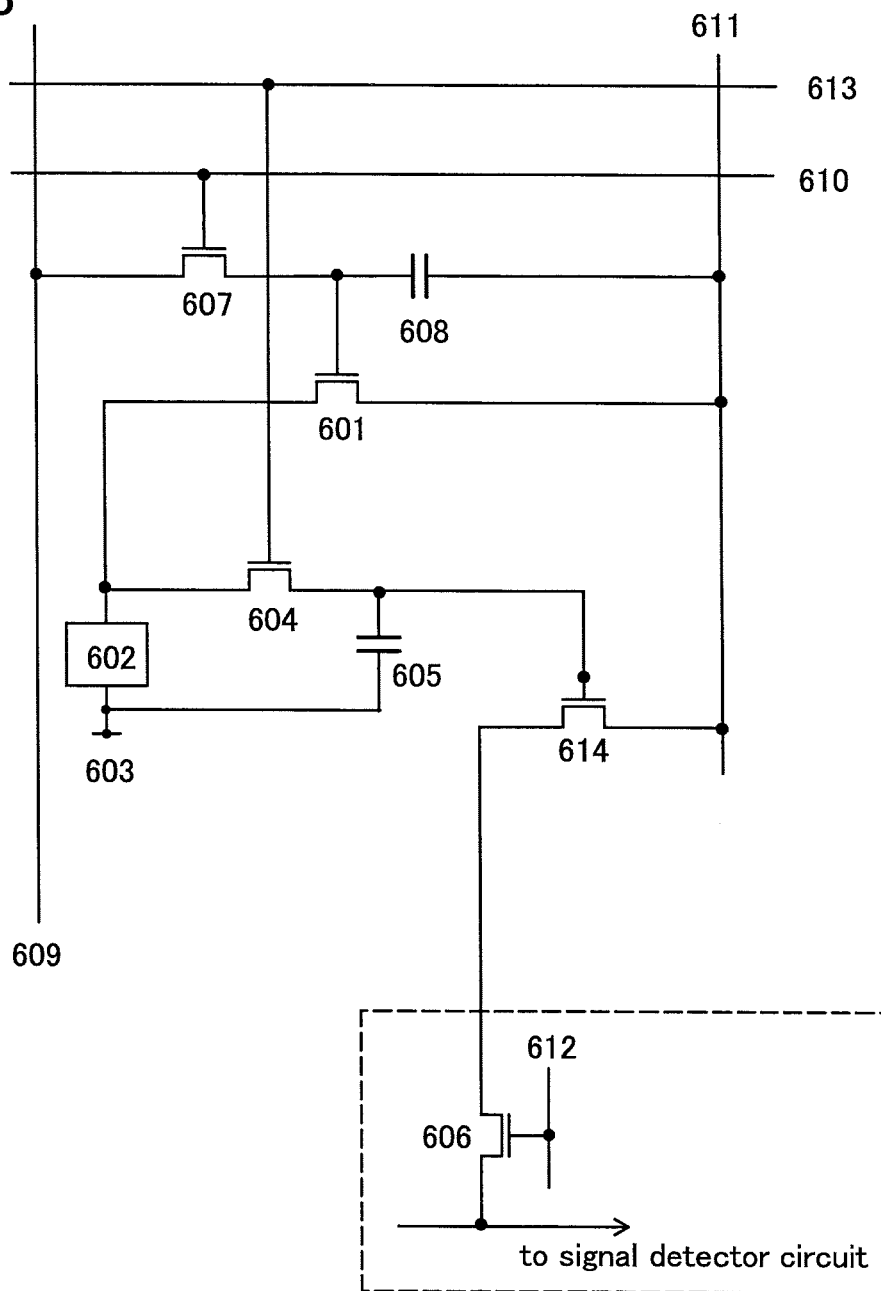


FIG. 14

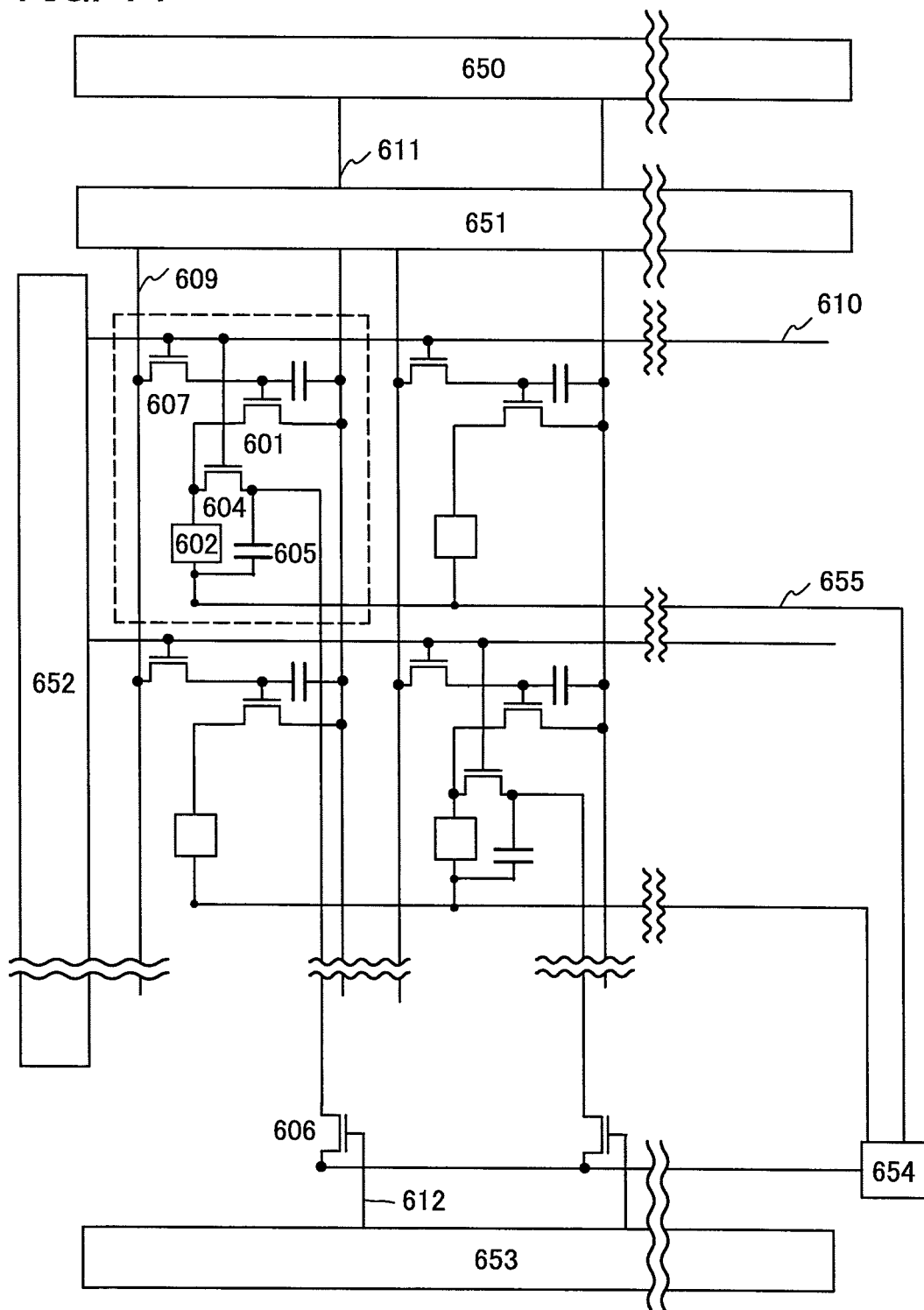


FIG. 15

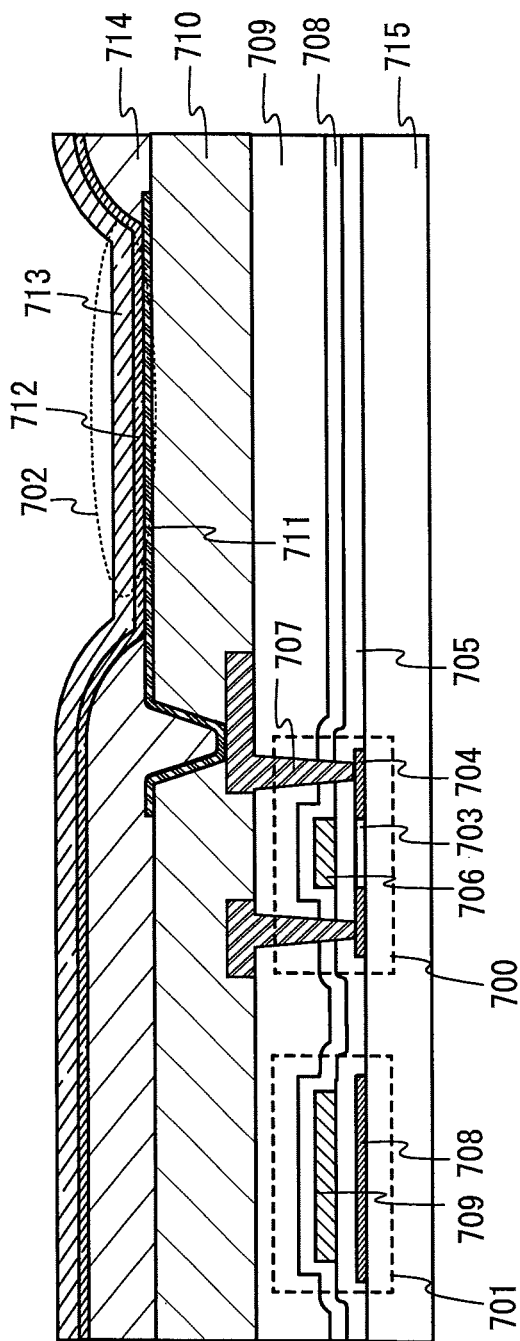


FIG. 16A

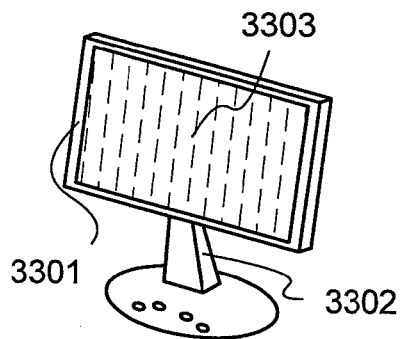


FIG. 16B

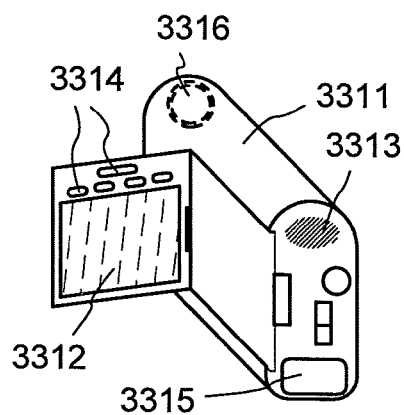


FIG. 16C

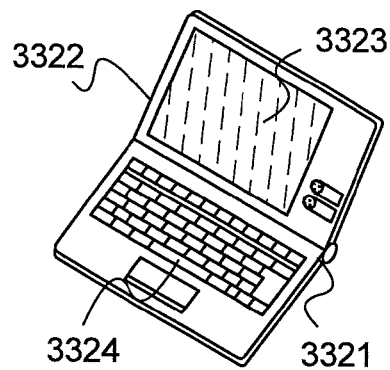


FIG. 16D

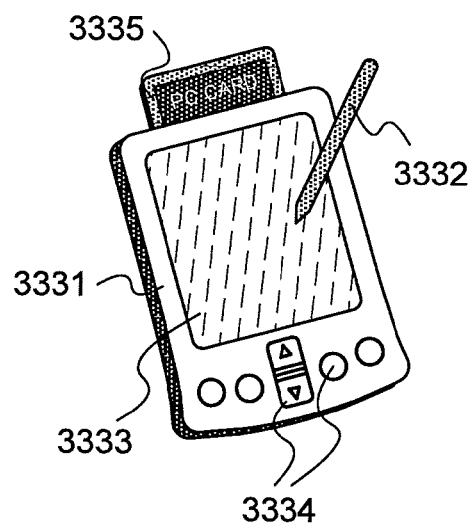


FIG. 16E

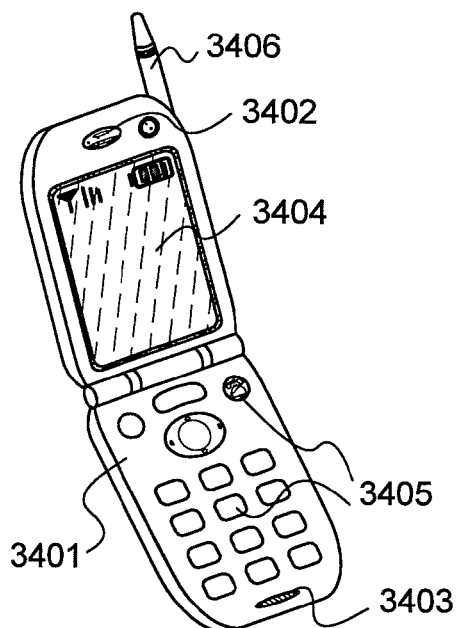


FIG. 16F

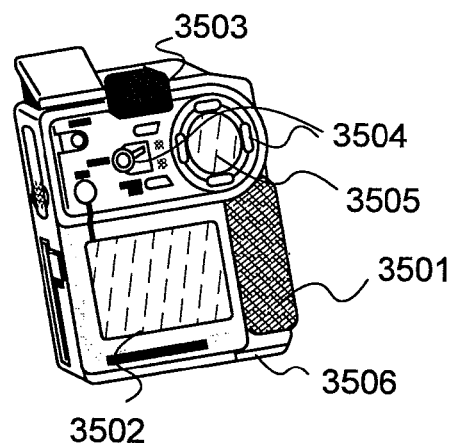
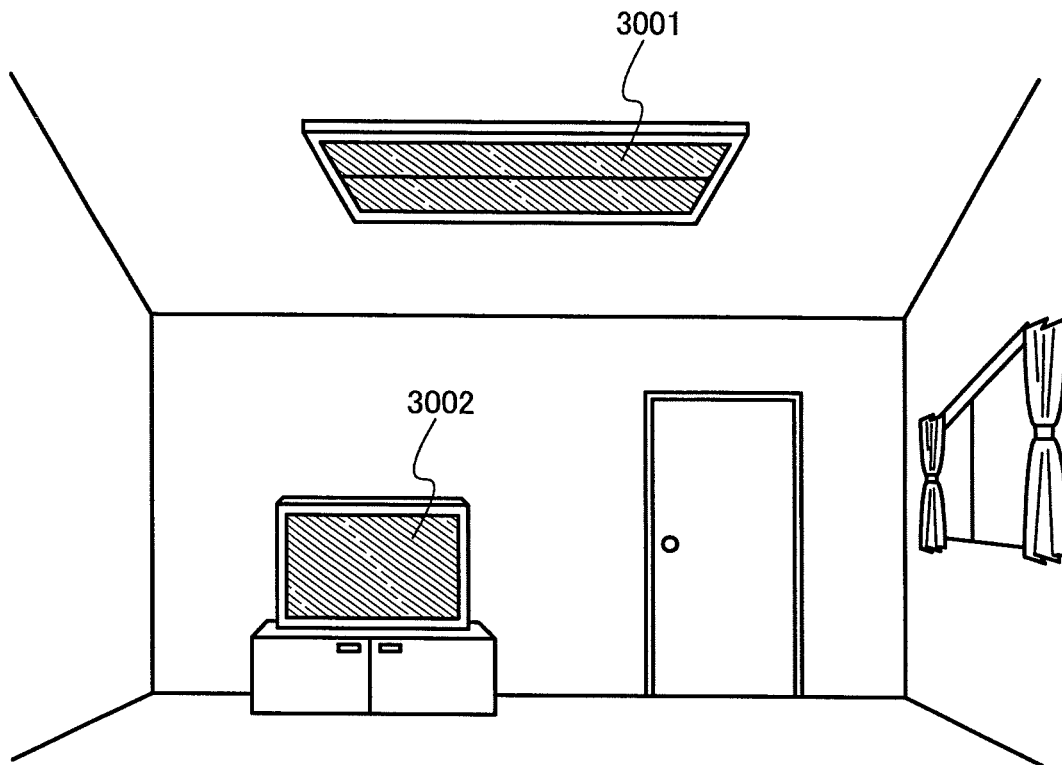


FIG. 17



LIGHT-EMITTING DEVICE AND DRIVING METHOD THEREOF

This application is a divisional of copending U.S. application Ser. No. 12/501,837 filed on Jul. 13, 2009.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a light-emitting device for compensating reduction in luminance of the light-emitting device.

2. Description of the Related Art

In recent years, wide-viewing-angle, high-moving-image-characteristics light-emitting devices using electroluminescence elements (EL elements) have been developed. The EL elements, which are self-emission elements that themselves emit light, have a problem in that the luminance is likely to decrease over time. When EL elements deteriorates, resistance thereof generally increases. Therefore, under a condition in which a certain voltage is applied to an EL element, the amount of current which flows into the EL element decreases as the EL element deteriorates, which cause reduction in the luminance.

In FIG. 1, a driving transistor **101** and an EL element **102** which is electrically connected to the driving transistor **101** are shown. A gate of the driving transistor **101** is electrically connected to a signal terminal **103**; one of a source and a drain of the driving transistor **101** is electrically connected to a first power source terminal **104**; the other of the source and the drain of the driving transistor **101** is electrically connected to one electrode (one of an anode and a cathode) of the EL element **102**; and the other electrode (the other of the anode and the cathode) of the EL element **102** is electrically connected to a second power source terminal **105**. High potential (or low potential) of a power source is applied to the first power source terminal **104**, and low potential (or high potential) of the power source is applied to the second power source terminal **105**. The driving transistor **101** controls the current which flows into the EL element **102** to determine the luminance of the EL element **102**. Description hereinbelow is made on the case where the driving transistor **101** is a p-channel transistor, but the present invention is not limited to this case of the p-channel transistor. The driving transistor **101** may be an n-channel transistor.

A curve **201** in FIG. 2A shows an I_{ds} (source-drain current) vs. V_{ds} (source-drain voltage) characteristic of a p-channel transistor. The curve **201** includes a saturation region **202** and a linear region **203**. When V_{ds} is equal to a value obtained by subtracting the threshold voltage (V_{th}) of the transistor from the gate-source voltage (V_{gs}), that is, $V_{ds}=V_{gs}-V_{th}$ (this V_{ds} is called a saturation drain voltage), V_{ds} delimits a boundary between the linear region **203** and the saturation region **202**. A dashed line **200** in FIG. 2A is a curve formed by a point which delimits the boundary between the linear region and the saturation region in the curve **201** when V_{gs} is changed. In other words, an intersection of the dashed line **200** and the curve which shows the I_{ds} vs. V_{ds} characteristic is a boundary point between the linear region and the saturation region.

In the case where the EL element **102** is driven with analog gray-scale displays, the driving transistor **101** is operated in the saturation region **202** in many cases. This is because, in the linear region, dependence on the gate voltage of the drain current is small, so that it is difficult to change the drain current significantly and it is not easy to drive the EL element with multiple gray-scale displays. Furthermore, this is because the dependence of I_{ds} on V_{ds} in the linear region **203** is larger than that in the saturation region **202**. Description will be made on this below.

In FIG. 2B, a current-voltage curve (I-V curve) **204** of the EL element **102** is shown in addition to the transistor characteristic shown in FIG. 2A. Reference symbol V_{com} denotes a reference potential of the EL element **102**. An intersection **206** of the curve **204** and the curve **201** corresponds to an operation point of the EL element **102**. In other words, a current I_{ds} corresponding to the intersection **206** flows into the EL element.

Deterioration of the EL element **102** increases the resistance of the EL element **102**. Then, the current-voltage curve (I-V curve) of the EL element **102** is changed from the curve **204** to a curve **205**. In accordance with this change, the operation point of the EL element **102** is shifted from the intersection **206** to an intersection **207**. In the saturation region **202**, the dependence of I_{ds} on V_{ds} is small, and therefore the amount of current (I_{ds}) flowing into the EL element **102** is not changed so much even if the I-V curve is changed from the curve **204** to the curve **205** due to the deterioration of the EL element by which the operation point is shifted from the intersection **206** to the intersection **207**. On the other hand, in the linear region **203** in which the dependence of I_{ds} on V_{ds} is large, the amount of current (I_{ds}) flowing into the EL element **102** is significantly changed when the EL element **102** deteriorates. Therefore, it is difficult to appreciate reduction in luminance of the EL element **102** when it is driven in the saturation region **202**.

However, when the EL element **102** significantly deteriorates, the I-V curve of the EL element **102** is changed from the curve **204** to a curve **208**, so that the operation point of the EL element **102** is shifted from the intersection **206** to an intersection **209**. The intersection **206** is positioned in the saturation region **202** whereas the intersection **209** is positioned in the linear region **203**, and therefore the amount of current which flows into the EL element **102** is largely changed to be reduced by ΔI in FIG. 2B. As a result, the luminance of the EL element is largely changed (FIG. 2B).

Patent Documents 1 and 2 are given as techniques for controlling the luminance of EL elements when the EL elements deteriorate.

In Patent Document 1, a display device has been disclosed in which two driving transistors having different characteristics are connected to an EL element and a means for selecting either one of the two driving transistors is provided so as to suppress the shift of the operation point of the EL element from the saturation region to the linear region due to deterioration of the EL element. For high-gray-level (high-luminance) display, a driving transistor having a capability of conducting high current is selected and a gate voltage of the driving transistor is decreased; and for low-gray-level (low-luminance) display, a driving transistor having a capability of conducting low current is selected.

Disclosed in Patent Document 2 is that a voltage between terminals of one EL element among a plurality of EL elements is detected and a voltage which is applied to a power source line is changed based on the detected voltage so that the luminances of the plurality of EL elements are controlled.

Patent Document

Patent Document 1: Japanese Published Patent Application No. 2004-341368

Patent Document 2: Japanese Published Patent Application No. 2006-47668

SUMMARY OF THE INVENTION

In the technology disclosed in Patent Document 1, the driving transistors having different current supply capabilities are manufactured separately depending on their respective sizes or structures. Thus, the current supply capabilities

of the driving transistors are fixed. Consequently, reduction in luminance of an EL element cannot be suppressed when deterioration of the EL element is large. Further, although it is preferable that V_{ds} be lower in considering the reliability of each driving transistor and the operation point of the EL element be positioned in the saturation region as near as possible to the linear region, flexibly setting the operation point of the EL element closer to the linear region in order to decrease V_{ds} is difficult because the current supply capabilities of the driving transistors are fixed. That is, considering the deterioration of the EL element sufficiently, it is necessary that the operation point of the EL element is apart from the linear region as far as possible, which results in an increase in V_{ds} , so that deterioration of the driving transistor is larger. As the driving transistor deteriorates, e.g., as the threshold voltage thereof is increased, the amount of current which flows into the EL element is decreased, in accordance with which the luminance of the EL element decreases.

In the invention disclosed in Patent Document 2, since the current flowing between the terminals of the EL element is detected during the period in which the EL element emits light, the amount of current which flows into the EL element is significantly decreased, so that the luminance decreases.

In view of the foregoing, it is an object of the present invention to provide a technique for controlling the luminance of EL elements without deterioration of driving transistors and without decrease in the amount of current which flows into the EL elements when the EL elements emit light so much.

As described above, considering the reliability of the driving transistor, it is preferable that the voltage V_{ds} which is applied to the driving transistor be low. Therefore, it is preferable that the operation point of the EL element be positioned in the saturation region so as not to be apart from the linear region so much. However, as the operation point of the EL element is set closer to the linear region, the operation point of the EL element is shifted from the saturation region to the linear region more easily as the EL element deteriorates.

As shown in FIG. 3A, when the operation point of the EL element shifts from the intersection **206** to the intersection **209** due to deterioration of the EL element, the source-drain voltage of the transistor is decreased by $\Delta V_{ds}=V_{ds}-V_{ds}'$. Whereas the voltage which is applied to the EL element is increased by $\Delta V_{EL}=V_{EL}-V_{EL}'$.

By returning the operation point of the EL element to the operation point being before the deterioration of the EL element, the amount of current which flows into the EL element is recovered, thereby returning the luminance of the EL element to the luminance being before the deterioration of the EL element. One method thereof is: a voltage V_{EL} and a voltage V_{EL}' , which are applied to the EL element before the deterioration of the EL element and after the deterioration of the EL element, respectively, are monitored, and the power source potential of the EL element (which is a reference potential of the EL element) is increased in the negative or positive direction by the same amount as a potential difference ΔV_{EL} therebetween. For example, in the case where the EL element is driven using a p-channel transistor, a reference potential V_{com} is increased by ΔV_{EL} or more in the negative direction. Accordingly, the I-V curve of the EL element shown in FIG. 3A can be shifted in parallel in the negative direction with respect to the voltage indicated in the horizontal axis, in accordance with which the operation point of the EL element can shift.

FIG. 3B illustrates an example in which the reference potential of the EL element is increased in the negative direc-

tion to return the operation point of the EL element being after the deterioration of the EL element to the saturation region being before the deterioration. In FIG. 3B, a curve of the current-voltage characteristic of the EL element is shifted from a curve **208** to a curve **210**. The operation point of the EL element is shifted from the intersection **209** in the linear region to an intersection **211** in the saturation region. A curve of the diode characteristic of the EL element is not simply shifted in parallel when the EL element is deteriorated. Therefore, the operation point of the EL element is not returned to the same point as the operation point being before the deterioration even by increasing the reference potential by ΔV_{com} . However, it is not necessary to return the operation point to the same point as the operation point being before the deterioration; the operation point only have to be returned from the linear region to the saturation region. This is because as long as the operation point of the EL element is returned to the saturation region, the current which flows into the EL element can be recovered to substantially the same amount as the amount of the current being before the deterioration, regardless of the position of the operation point in the saturation region. This means that the tolerance of the change amount of the reference potential is wide and the amount of current which flows into the EL element can be easily controlled.

Another method for recovering the amount of current which flows into the EL element is: the gate-source voltage of the driving transistor is increased, which enables the amount of current which flows into the EL element to be recovered to the amount of current being before the deterioration. However, even when the source-line potential is increased, the operation point of the EL element remains in the linear region, so that the drain current which flows into the driving transistor in the linear region, that is, the current which flows into the EL element depends significantly on the source-drain voltage; therefore, it is difficult to determine the amount of current which flows into the EL element by controlling the source-line potential. Accordingly, it is easier to control the current which flows into the EL element by increasing the reference potential of the EL element.

In view of the above, the potential difference which is applied between electrodes of the EL element before and after the deterioration are detected and the reference potential of the EL element is changed, thereby compensating for the luminance of the EL element.

Structures of embodiments of the present invention will be described below.

One embodiment of the present invention is: the potential difference which is applied between the electrodes of the EL element is detected at the time of light emission of the EL element, so that the luminance of the EL element is compensated. Charge corresponding to the potential difference between the electrodes is accumulated in a storage capacitor, the degree of deterioration of the EL element is calculated based on the charge, and the power source potential or reference potential of the EL element is changed, so that the luminance of the EL element is compensated. After the charge corresponding to the potential difference between the electrodes is accumulated, light emission of the EL element is decayed and the potential difference which is applied between the electrodes of the EL element is detected, or alternatively, at a time of light emission of the EL element, the potential difference is detected; in this manner, the luminance of the EL element is compensated.

A circuit according to one embodiment of the present invention includes a driving transistor, an EL element, and a first transistor. A gate of the driving transistor is electrically

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connected to a first signal terminal; one of a source and a drain thereof is electrically connected to a first power source terminal; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the first transistor and one electrode (one of an anode and a cathode) of the EL element. A gate of the first transistor is electrically connected to a second signal terminal; and the other of the source and the drain of the first transistor is electrically connected to a signal detector circuit. The other electrode (the other of the anode and the cathode) of the EL element is electrically connected to a second power source terminal. The first power source terminal and the second power source terminal may be connected to power sources independent of each other; or alternatively, the first power source terminal may be electrically connected to the high potential side (or low potential side) of a power source and the second power source terminal may be electrically connected to the low potential side (or high potential side) of the power source.

The driving transistor is turned on by application of the potential of the first signal terminal to supply the potential of the first power source terminal to the EL element, so that the EL element emits light. The first transistor detects the potential difference or the amount of current between the electrodes of the EL element. In a period in which the EL element emits light, the first transistor is turned on by application of the potential of the second signal terminal, thereby conducting charge corresponding to the potential difference between the electrodes of the EL element to the signal detector circuit through the first transistor as a signal current or a signal potential (Vout). In this manner, the potential difference between the electrodes of the EL element is detected. In view of the change in the detected potential difference of the EL element, the potential of the second power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element.

A circuit according to one embodiment of the present invention includes a driving transistor, an EL element, a first transistor, a second transistor, and a storage capacitor. A gate of the driving transistor is electrically connected to a first signal terminal; one of a source and a drain thereof is electrically connected to a first power source terminal; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the first transistor and one electrode of the EL element. A gate of the first transistor is electrically connected to a second signal terminal; and the other of the source and the drain of the first transistor is electrically connected to one electrode of the storage capacitor and one of a source and a drain of the second transistor. The other electrode of the storage capacitor is electrically connected to the other electrode of the EL element and a second power source terminal. A gate of the second transistor is electrically connected to a third signal terminal; and the other of the source and the drain of the second transistor is electrically connected to a signal detector circuit. The first power source terminal and the second power source terminal may be connected to power sources independent of each other; or alternatively, the first power source terminal may be electrically connected to the high potential side (or low potential side) of a power source and the second power source terminal may be electrically connected to the low potential side (or high potential side) of the power source.

The driving transistor is turned on by application of the potential of the first signal terminal to supply the potential of the first power source terminal to the EL element, so that the EL element emits light. In a period in which the EL element emits light, the first transistor is turned on by application of

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the potential of the second signal terminal, thereby accumulating charge corresponding to the potential difference between the electrodes of the EL element in the storage capacitor. Then, the first transistor is turned off by application of the potential of the second signal terminal, so that the charge accumulated in the storage capacitor is retained. Following this state, the driving transistor is turned off by application of the potential of the first signal terminal to decay light emission of the EL element. After that, the second transistor is turned on by application of the potential of the third signal terminal, thereby conducting the charge accumulated in the storage capacitor to the signal detector circuit through the second transistor as a signal current or a signal potential. Then, in view of the change in the detected potential difference which is applied to the EL element, the potential of the second power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the storage capacitor functions as a memory element which retains the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element can be detected even in the state where the EL element does not emit light. Therefore, without reduction in the luminance at the time of light emission of the EL element, the potential of the second power source terminal connected to the other electrode of the EL element can be controlled in view of the change in the potential difference which is applied to the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. Further alternatively, the first transistor and the second transistor can be turned on during the period in which the EL element emits light, thereby detecting the potential difference between the electrodes of the EL element. However, it is necessary to detect the potential difference as fast as possible such that the luminance of the EL element is not adversely affected. Further, it is preferable that the impedance of the detection side of the signal detector circuit is high enough not to change the potential of the electrode of the EL element.

A circuit according to one embodiment of the present invention includes a driving transistor, an EL element, a first transistor, a second transistor, and a storage capacitor. A gate of the driving transistor is electrically connected to a first signal terminal; one of a source and a drain thereof is electrically connected to a first power source terminal; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the first transistor and one electrode of the EL element. A gate of the first transistor is electrically connected to a second signal terminal; and the other of the source and the drain of the first transistor is electrically connected to one electrode of the storage capacitor and a gate of the second transistor. The other electrode of the storage capacitor is electrically connected to the other electrode of the EL element and a second power source terminal. One of a source and a drain of the second transistor is electrically connected to the first power source terminal; and the other of the source and the drain of the second transistor is electrically connected to a signal detector circuit. The first power source terminal and the second power source terminal may be connected to power sources independent of each other; or alternatively, the first power source terminal may be electrically connected to the high potential side (or low potential side) of a power source and the second power source terminal may be electrically connected to the low potential side (or high potential side) of the power source.

The driving transistor is turned on by application of the potential of the first signal terminal to supply the potential of

the first power source terminal to the EL element, so that the EL element emits light. In a period in which the EL element emits light, the first transistor is turned on by application of the potential of the second signal terminal, thereby accumulating charge corresponding to the potential difference between the electrodes of the EL element in the storage capacitor and supplying the potential of one electrode of the EL element to the gate of the second transistor to turn on the second transistor. At this time, the second transistor conducts the potential of one electrode of the EL element which is retained by the storage capacitor to the signal detector circuit while suppressing deterioration (generation of noise). Then, the first transistor is turned off by application of the potential of the second signal terminal, so that the charge accumulated in the storage capacitor is retained. Following this state, the driving transistor is turned off by application of the potential of the first signal terminal to decay light emission of the EL element. With the second transistor, the potential of the one electrode of the EL element is conducted to the signal detector circuit as a signal current or a signal potential. Then, in view of the change in the detected potential difference which is applied to the EL element, the potential of the second power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the storage capacitor functions as a memory element which retains the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element can be detected even in the state where the EL element does not emit light. Therefore, without reduction in the luminance at the time of light emission of the EL element, the potential of the second power source terminal connected to the other electrode of the EL element can be controlled in view of the change in the potential difference which is applied to the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. Further alternatively, the first transistor and the second transistor can be turned on during the period in which the EL element emits light, thereby detecting the potential difference between the electrodes of the EL element. However, it is necessary to detect the potential difference as fast as possible such that the luminance of the EL element is not adversely affected. Further, it is preferable that the impedance of the detection side of the signal detector circuit is high enough not to change the potential of the electrode of the EL element.

A circuit according to one embodiment of the present invention includes a driving transistor, an EL element, a first transistor, a second transistor, a third transistor, and a storage capacitor. A gate of the driving transistor is electrically connected to a first signal terminal; one of a source and a drain thereof is electrically connected to a first power source terminal; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the first transistor and one electrode of the EL element. A gate of the first transistor is electrically connected to a second signal terminal; and the other of the source and the drain of the first transistor is electrically connected to one electrode of the storage capacitor and a gate of the second transistor. The other electrode of the storage capacitor is electrically connected to the other electrode of the EL element and a second power source terminal. One of a source and a drain of the second transistor is electrically connected to the first power source terminal; and the other of the source and the drain of the second transistor is electrically connected to one of a source and a drain of the third transistor. A gate of the third transistor is electrically connected to a third signal terminal, and the

other of the source and the drain of the third transistor is electrically connected to a signal detector circuit. The first power source terminal and the second power source terminal may be connected to power sources independent from each other; or alternatively, the first power source terminal may be electrically connected to the high potential side (or low potential side) of a power source and the second power source terminal may be electrically connected to the low potential side (or high potential side) of the power source.

The driving transistor is turned on by application of the potential of the first signal terminal to supply the potential of the first power source terminal to the EL element, so that the EL element emits light. In a period in which the EL element emits light, the first transistor is turned on by application of the potential of the second signal terminal, thereby accumulating charge corresponding to the potential difference between the electrodes of the EL element in the storage capacitor and supplying the potential of one electrode of the EL element to the gate of the second transistor to turn on the second transistor. At this time, the second transistor conducts the potential of one electrode of the EL element which is retained by the storage capacitor to the signal detector circuit while suppressing deterioration (generation of noise). Then, the first transistor is turned off by application of the potential of the second signal terminal, so that the charge accumulated in the storage capacitor is retained. Following this state, the driving transistor is turned off by application of the potential of the first signal terminal to decay light emission of the EL element. Next, the third transistor is turned on by application of the potential of the third signal terminal to conduct the potential of one electrode of the EL element to the signal detector circuit as a signal current or a signal potential. Then, in view of the change in the potential difference between the electrodes of the EL element, which is detected in the signal detector circuit, the potential of the second power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the storage capacitor functions as a memory element which retains the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element can be detected even in the state where the EL element does not emit light. Therefore, without reduction in the luminance at the time of light emission of the EL element, the potential of the second power source terminal connected to the other electrode of the EL element can be controlled in view of the change in the potential difference which is applied to the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. Further alternatively, the first transistor and the second transistor can be turned on during the period in which the EL element emits light, thereby detecting the potential difference between the electrodes of the EL element. However, it is necessary to detect the potential difference as fast as possible such that the luminance of the EL element is not adversely affected. Further, it is preferable that the impedance of the detection is high enough not to change the potential of the electrode of the EL element.

An active matrix circuit according to one embodiment of the present invention includes a driving transistor, an EL element, a first transistor, a second transistor, a first storage capacitor, a switching transistor, a second storage capacitor, a first scanning line, a second scanning line, a signal line, and a power source line. A gate of the switching transistor is electrically connected to the first scanning line; one of a source and a drain thereof is electrically connected to the signal line; and the other of the source and the drain thereof is electrically

connected to a gate of the driving transistor and one electrode of the second storage capacitor. One of a source and a drain of the driving transistor is electrically connected to the power source line and the other electrode of the second storage capacitor; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the first transistor and one electrode of the EL element. A gate of the first transistor is electrically connected to the first scanning line; and the other of the source and the drain of the first transistor is electrically connected to one electrode of the first storage capacitor and one of a source and a drain of the second transistor. The other electrode of the first storage capacitor is electrically connected to the other electrode of the EL element and a power source terminal. A gate of the second transistor is electrically connected to the second scanning line; and the other of the source and the drain of the second transistor is electrically connected to a signal detector circuit. The power source line is electrically connected to one of the high potential side and the low potential side of a power source whereas the power source terminal is electrically connected to the other of the low potential side and the high potential side of the power source.

Either the second transistor or the second scanning line is not necessarily provided per pixel but may be provided per row or column of pixels.

The switching transistor is turned on by application of the potential of the first scanning line to supply the potential of the signal line to one electrode of the second storage capacitor and the gate of the driving transistor. The second storage capacitor retains the gate potential of the driving transistor. When the driving transistor is turned on, the potential of the power source line is supplied to the EL element and the EL element emits light. The potential of the first scanning line turns on the switching transistor and the first transistor. During the period in which the first transistor is on, charge corresponding to the potential difference which is applied to the EL element is accumulated in the first storage capacitor. Next, the switching transistor and the first transistor are turned off, so that the charge is retained in the first storage capacitor. Next, the second transistor is turned on by application of the potential of the second scanning line, so that the charge accumulated in the first storage capacitor is conducted through the second transistor to the signal detector circuit as a signal current or a signal potential, whereby the potential difference between the electrodes of the EL element is detected. In view of the change in the detected potential difference which is applied to the EL element, the potential of the power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the first storage capacitor functions as a memory element which retains the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element can be detected even in the state where the EL element does not emit light. Therefore, without reduction in the luminance at the time of light emission of the EL element, the potential of the power source terminal connected to the other electrode of the EL element can be controlled in view of the change in the potential difference which is applied to the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. Further alternatively, during the period in which the switching transistor and the first transistor are on where the EL element emits light, the potential difference between the electrodes of the EL element can be detected. However, it is

necessary to detect the potential difference as fast as possible such that the luminance of the EL element is not adversely affected.

The switching transistor and the first transistor are controlled by the first scanning line, but may be controlled by different scanning lines.

An active matrix circuit according to one embodiment of the present invention includes a driving transistor, an EL element, a first transistor, a second transistor, a third transistor, a first storage capacitor, a switching transistor, a second storage capacitor, a first scan line, a second scan line, a signal line, and a power source line. A gate of the switching transistor is electrically connected to the first scanning line; one of a source and a drain thereof is electrically connected to the signal line; and the other of the source and the drain thereof is electrically connected to a gate of the driving transistor and one electrode of the second storage capacitor. One of a source and a drain of the driving transistor is electrically connected to the power source line and the other electrode of the second storage capacitor; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the first transistor and one electrode of the EL element. A gate of the first transistor is electrically connected to the first scanning line; and the other of the source and the drain of the first transistor is electrically connected to one electrode of the first storage capacitor and a gate of the third transistor. The other electrode of the first storage capacitor is electrically connected to the other electrode of the EL element and a power source terminal. One of a source and a drain of the third transistor is electrically connected to the power source line; and the other of the source and the drain of the third transistor is electrically connected to one of a source and a drain of the second transistor. A gate of the second transistor is electrically connected to the second scanning line, and the other of the source and the drain of the second transistor is electrically connected to a signal detector circuit. The power source line is electrically connected to one of the high potential side and the low potential side of a power source whereas the power source terminal is electrically connected to the other of the high potential side and the low potential side of the power source.

Either the second transistor or the second scan line is not necessarily provided per pixel but may be provided per row or column of pixels.

The switching transistor is turned on by application of the potential of the first scan line to supply the potential of the signal line to the second storage capacitor and the gate of the driving transistor. The second storage capacitor retains the gate potential of the driving transistor. When the driving transistor is turned on, the potential of the power source line is supplied to the EL element and the EL element emits light. The potential of the first scanning line turns on the switching transistor and the first transistor. During the period in which the first transistor is on, charge corresponding to the potential difference which is applied to the EL element is accumulated in the first storage capacitor and the potential of one electrode of the EL element is also applied to the gate of the third transistor to turn on the third transistor. At this time, the third transistor conducts the potential difference between the electrodes of the EL element, which is retained by the storage capacitor, to the signal detector circuit while suppressing deterioration (generation of noise). Next, the switching transistor and the first transistor are turned off by application of the potential of the first scanning line, so that the charge is retained in the first storage capacitor. Next, the switching transistor is turned on by application of the potential of the second scanning line, so that the potential of one electrode of

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the EL element is conducted to the signal detector circuit as a signal current or a signal potential. Then, in view of the detected potential difference between the electrodes of the EL element, the potential of the power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the first storage capacitor functions as a memory element which retains the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element can be detected even in the state where the EL element does not emit light. Therefore, without reduction in the luminance at the time of light emission of the EL element, the potential of the power source terminal connected to the other electrode of the EL element can be controlled in view of the change in the potential difference of the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. Further alternatively, during the period in which the switching transistor and the first transistor are on where the EL element emits light, the potential difference between the electrodes of the EL element can be detected. However, it is necessary to detect the potential difference as fast as possible such that the luminance of the EL element is not adversely affected. Further, it is preferable that the impedance of the detection is high enough not to change the potential of the electrode of the EL element.

The switching transistor and the first transistor are controlled by the first scan line, but may be controlled by different scanning lines.

The conductivity types of the driving transistor, the first transistor, the second transistor, the third transistor, and the switching transistor may be individually either an n-type or a p-type.

According to one mode of the present invention, in order to compensate the reduction in luminance due to the deterioration of the EL element, the potential difference between the electrodes of the EL element is detected in the light-emitting period of the EL element, charge corresponding to the potential difference between the electrodes is accumulated in the storage capacitor, the degree of deterioration of the EL element is calculated based on this charge, and the power source potential or the reference potential of the EL element is changed. After the charge corresponding to this potential difference is accumulated in the storage capacitor, the light emission of the EL element may be decayed; or alternatively, the potential difference between the electrodes of the EL element is detected in the period in which the EL element emits light, so that the luminance of the EL element is compensated. In this manner, reduction in luminance due to decrease in the amount of current which flows into the EL element can be prevented. Further, the operation point of the driving transistor which is operated in the saturation region can be shifted to be closer to the linear region, and the voltage which is applied to the driving transistor can be decreased to suppress the deterioration of the characteristics of the driving transistor.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a circuit diagram of an EL element.

FIGS. 2A and 2B are graphs of characteristic curves.

FIGS. 3A and 3B are graphs of characteristic curves.

FIGS. 4A and 4B are circuit diagrams of light-emitting devices according to Embodiment 1 of the present invention.

FIG. 5 is a timing chart according to Embodiment 1 of the present invention.

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FIG. 6 is a timing chart according to Embodiment 1 of the present invention.

FIGS. 7A and 7B are circuit diagrams of light-emitting devices according to Embodiment 2 of the present invention.

FIG. 8 is a timing chart according to Embodiment 2 of the present invention.

FIG. 9 is a circuit diagram of a light-emitting device according to Embodiment 3 of the present invention.

FIG. 10 is a timing chart according to Embodiment 3 of the present invention.

FIG. 11 is a circuit diagram of the light-emitting device according to Embodiment 3 of the present invention.

FIG. 12 is a circuit diagram of a light-emitting device according to Embodiment 4 of the present invention.

FIG. 13 is a circuit diagram of the light-emitting device according to Embodiment 4 of the present invention.

FIG. 14 is a circuit diagram of a light-emitting device according to Embodiment 5 of the present invention.

FIG. 15 is a cross-sectional view of a light-emitting device according to Embodiment 6 of the present invention.

FIGS. 16A to 16F are views each illustrating an example of an electronic apparatus according to Embodiment 7 of the present invention.

FIG. 17 is a view showing an example of an electronic apparatus according to Embodiment 7 of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

Embodiments of the present invention will be described with reference to the drawings. However, the present invention can be implemented in many different modes other than these, and it is to be easily understood by those skilled in the art that various changes in modes and details thereof can be changed variously without departing from the purpose and scope of the present invention. Therefore, the present invention should not be interpreted as being limited to the description of the embodiments to be given below. Further, the same portions and portions having the same functions are denoted by the same reference numerals through the drawings; and the description will be not repeated in the description hereinbelow.

Embodiment 1

In FIG. 4A, a driving transistor **401**, an EL element **402**, and a first transistor (SW-1 Tr) **501** are shown. A gate of the driving transistor **401** is electrically connected to a first signal terminal **403**. One of a source and a drain of the driving transistor **401** is electrically connected to a first power source terminal **404**; and the other of the source and the drain thereof is electrically connected to one electrode (one of an anode and a cathode) of the EL element **402** and one of a source and a drain of the SW-1 Tr **501**. A gate of the SW-1 Tr **501** is electrically connected to a second signal terminal **406**; and the other of the source and the drain thereof is electrically connected to a signal detector circuit. The other electrode (the other of the anode and the cathode) of the EL element **402** is electrically connected to a second power source terminal **405**.

The driving transistor **401** controls the amount of current which flows into the EL element **402** to determine the luminance of the EL element **402**. A power source potential (Vdd) is applied to the first power source terminal **404**, and a reference potential (Vcom) is applied to the second power source terminal **405**.

The SW-1 Tr **501** functions as a switch when the potential of one electrode of the EL element **402** is conducted to the

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signal detector circuit. The SW-1 Tr 501 is turned on by the potential of the second signal terminal 406, thereby conducting the potential of one electrode (one of the anode and the cathode) of the EL element 402 to the signal detector circuit through the SW-1 Tr 501 as a signal current or a signal potential (Vout). In this manner, the potential difference between the electrodes of the EL element 402 can be detected. In view of the change in the detected potential difference of the EL element 402, the reference potential (Vcom) which is applied to the second power source terminal 405 connected to the other electrode of the EL element 402 is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element 402.

The operation of the circuit shown in FIG. 4A will be described using a timing chart shown in FIG. 5. The driving transistor 401 functions as a switch for supplying current to the EL element 402. A potential Vg1 is conducted to the first signal terminal 403. When Vg1 is higher than the threshold voltage of the driving transistor 401, the driving transistor 401 is turned on to conduct the power source potential Vdd to one electrode of the EL element 402, so that a voltage (V_{EL}) which is the potential difference between the power source potential Vdd and the potential of the second power source terminal 405 is applied to the EL element. As a result, the EL element 402 emits light. On the other hand, when Vg1 is lower than the threshold voltage of the driving transistor 401, the driving transistor 401 is turned off not to conduct the power source potential Vdd to the EL element, so that the EL element 402 does not emit light.

The driving transistor 401 is turned on by application of the potential Vg1 of the first signal line to conduct the potential V_{EL} between the electrodes of the EL element 402, so that the EL element 402 emits light. Next, the SW-1 Tr 501 is turned on by application of a potential Vg2 of the second signal line, thereby conducting the potential of one electrode of the EL element 402 to the signal detector circuit as a signal current or a signal potential (Vout). The SW-1 Tr 501 is turned on only at a time in the period in which the EL element 402 emits light. Note that ON/OFF of the SW-1 Tr 501 can be changed by changing the potential Vg2 of the second signal terminal 406: when Vg2 is higher than the threshold voltage of the SW-1 Tr 501, the SW-1 Tr 501 is turned on whereas when Vg2 is lower than the threshold voltage of the SW-1 Tr 501, the SW-1 Tr 501 is turned off. During the period in which the driving transistor 401 is turned on and the EL element 402 emits light, the SW-1 Tr 501 is turned on. As shown in FIG. 3B, as the EL element deteriorates, the voltage which is applied to the EL element is increased by $\Delta V_{EL} = V_{EL} - V_{EL'}$. The signal detector circuit detects the voltage which is applied to the EL element and ΔV_{EL} is calculated, and the reference potential of the EL element is increased by ΔV_{com} where $\Delta V_{com} > \Delta V_{EL}$. Accordingly, the amount of current which flows into the EL element can be recovered, so that the luminance of the EL element can be returned to the luminance being before the deterioration of the EL element. In FIG. 5, the state where the voltage which is higher by ΔV_{com} is applied between the electrodes of the EL element at the timing before the EL element emits light next is shown.

The potential difference between the electrodes of the EL element before deterioration, which is a reference value for compensation of the luminance of the EL element, can be detected at any timing as appropriate: for example, at the time when power is on, or for each period of time.

According to this circuit, the voltage which is applied to the EL element 402 can be detected in a part of period in which the driving transistor 401 is turned on, that is, the EL element 402 emits light. Therefore, the voltage which is applied to the

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EL element 402 can be detected without reduction in the amount of current which flows into the EL element or reduction in the luminance of the EL element.

In the circuit shown in FIG. 4A, the potential difference between the electrodes of the EL element is detected only in the period in which the SW-1 Tr is turned on. However, charge corresponding to the potential difference between the electrodes of the EL element may be accumulated in a storage capacitor (Cs), and then, the accumulated charge may be conducted to the signal detector circuit as a signal current or a signal potential (Vout) (FIG. 4B).

In FIG. 4B, a driving transistor 401, an EL element 402, a SW-1 Tr 501, a second transistor (SW-2 Tr) 502, and a storage capacitor (Cs) 503 are shown. A gate of the driving transistor 401 is electrically connected to a first signal terminal 403. One of a source and a drain of the driving transistor 401 is electrically connected to a first power source terminal 404; and the other of the source and the drain thereof is electrically connected to one electrode of the EL element 402 and one of a source and a drain of the SW-1 Tr 501. A gate of the SW-1 Tr 501 is electrically connected to a second signal terminal 406; and the other of the source and the drain thereof is electrically connected to one electrode of the Cs 503 and one of a source and a drain of the SW-2 Tr 502. The other electrode of the Cs 503 is electrically connected to the other electrode of the EL element 402 and a second power source terminal 405. A gate of the SW-2 Tr 502 is electrically connected to a third signal terminal 407; and the other of the source and the drain of the SW-2 Tr 502 is electrically connected to a signal detector circuit.

The Cs 503 accumulates charge corresponding to the potential difference between the electrodes of the EL element 402. The SW-1 Tr 501 functions as a switch for supplying charge to the Cs 503. The SW-1 Tr 501 is selected (turned on) by the potential of the second signal terminal 406, so that the charge corresponding to the potential difference between the electrodes of the EL element 402 is accumulated in the Cs 503. Next, the SW-1 Tr 501 is turned off by application of the potential of the second signal terminal 406, so that the charge accumulated in the Cs 503 is retained. The Cs 503 functions as a memory element for retaining the potential difference between the electrodes of the EL element 402, and the potential difference between the electrodes of the EL element 402 can be conducted to the signal detector circuit by turning the SW-2 Tr 502 on by application of the potential of the third signal terminal 407 even in the period in which the EL element does not emit light. Therefore, without reduction in the luminance at the time of light emission of the EL element, the potential of the second power source terminal connected to the other electrode of the EL element can be controlled in view of the change in the potential difference which is applied to the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. Further alternatively, the SW-1 Tr 501 and the SW-2 Tr 502 can be turned on during the period in which the EL element emits light, thereby detecting the potential difference between the electrodes of the EL element. However, it is necessary to detect the potential difference as fast as possible such that the luminance of the EL element is not adversely affected. Further, it is preferable that the impedance of the detection side of the signal detector circuit is high enough not to change the potential of the electrode of the EL element.

The operation of the circuit shown in FIG. 4B will be described using a timing chart shown in FIG. 6. The driving transistor 401 functions as a switch for supplying current to the EL element 402. A potential Vg1 is conducted to the first signal terminal 403. When Vg1 is higher than the threshold

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voltage of the driving transistor **401**, the driving transistor **401** is turned on to conduct the power source potential Vdd to one electrode of the EL element **402**, so that a voltage (V_{EL}) which is the potential difference between the power source potential Vdd and the potential of the second power source terminal **405** is applied to the EL element **402**. As a result, the EL element **402** emits light. On the other hand, when Vg1 is lower than the threshold voltage of the driving transistor **401**, the driving transistor **401** is turned off not to conduct the power source potential Vdd to the EL element **402**, so that the EL element **402** does not emit light.

The driving transistor **401** is turned on by application of the potential Vg1 of the first signal line to conduct the potential V_{EL} between the electrodes of the EL element **402**, so that the EL element **402** emits light. Next, the SW-1 Tr **501** is turned on by application of a potential Vg2 of the second signal line, so that charge corresponding to the potential difference which is applied to the EL element **402** is accumulated in the Cs **503**. After the charge is accumulated in the Cs **503**, the SW-1 Tr **501** is turned off, so that the accumulated charge is retained in the Cs **503**.

Next, the driving transistor **401** is turned off by application of the potential Vg1 of the first signal line, so that the light emission of the EL element **402** is decayed. After that, the SW-2 Tr **502** is turned on by application of a potential Vg3 of the third signal line, thereby conducting the charge in the Cs **503** to the signal detector circuit as a signal current or a signal potential (Vout). The Cs **503** functions as a memory element for retaining the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element **402** can be conducted to the signal detector circuit by application of the potential of the third signal terminal **407** even in the period in which the EL element **402** does not emit light. As shown in FIG. 3B, as the EL element deteriorates, the voltage which is applied to the EL element is increased by $\Delta V_{EL} = V_{EL} - V_{EL}$. The signal detector circuit monitors the voltage which is applied to the EL element and ΔV_{EL} is calculated, and the reference potential of the EL element is increased by ΔV_{com} where $\Delta V_{com} > \Delta V_{EL}$. Accordingly, the amount of current which flows into the EL element can be recovered, so that the luminance of the EL element can be returned to the luminance being before the deterioration of the EL element. In FIG. 6, the state where the voltage which is higher by ΔV_{com} is applied between the electrodes of the EL element at the timing before the EL element emits light next is shown.

The potential difference between the electrodes of the EL element before deterioration, which is a reference value for compensation of the luminance of the EL element, can be detected at any timing as appropriate: for example, at the time when power is on, or for each period of time.

The conductivity types of the driving transistor **401**, the SW-1 Tr **501**, and the SW-2 Tr **502** are individually either an n-type or a p-type.

According to this circuit, the luminance of the EL element can be compensated without reduction in the current which flows into the EL element or the luminance of the EL element. An input load of the signal detector circuit side does not directly affect the light emission of the EL element, that is, display.

Embodiment 2

In the circuit in FIG. 4B, the gate of the SW-2 Tr **502** is electrically connected to the third signal terminal **407**, and the other of the source and the drain of the SW-1 Tr **501** and one electrode of the Cs **503** are electrically connected to one of the

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source and the drain of the SW-2 Tr **502**. The present invention is, however, not limited to this circuit. Without provision of the third signal terminal **407**, the other of the source and the drain of the SW-1 Tr **501** and one electrode of the Cs **503** may be electrically connected to the gate of the SW-2 Tr **502**, so that a signal corresponding to the potential difference of the electrodes of the EL element is conducted to the signal detector circuit (FIG. 7A).

A circuit shown in FIG. 7A includes a driving transistor **401**, an EL element **402**, a SW-1 Tr **501**, a SW-2 Tr **502**, and a Cs **503**. A gate of the driving transistor **401** is electrically connected to a first signal terminal **403**. One of a source and a drain of the driving transistor **401** is electrically connected to a first power source terminal **404**; and the other of the source and the drain thereof is electrically connected to one electrode of the EL element **402** and one of a source and a drain of the SW-1 Tr **501**. A gate of the SW-1 Tr **501** is electrically connected to a second signal terminal **406**; and the other of the source and the drain thereof is electrically connected to one electrode of the Cs **503** and a gate of the SW-2 Tr **502**. The other electrode of the Cs **503** is electrically connected to the other electrode of the EL element **402** and a second power source terminal **405**. One of a source and a drain of the SW-2 Tr **502** is electrically connected to the first power source terminal **404**; and the other of the source and the drain of the SW-2 Tr **502** is electrically connected to a signal detector circuit.

The functions and operations of the driving transistor **401** and the SW-1 Tr **501** are the same as those in Embodiment 1. A power source potential (Vdd) is conducted to the first power source terminal **404**, and a reference potential (Vcom) is conducted to the second power source terminal **405**.

During the period in which the driving transistor **401** is on and the EL element **402** emits light, the SW-1 Tr **501** is selected (turned on) by application of the potential of the second signal terminal **406**, thereby accumulating charge corresponding to the potential difference between the electrodes of the EL element **402** in the Cs **503** and conducting the potential of one electrode of the EL element **402** to the gate of the SW-2 Tr **502** to select the SW-2 Tr **502**. Accordingly, the potential difference between the electrodes of the EL element **402** is conducted to the signal detector circuit as a signal current or a signal potential. At this time, the SW-2 Tr **502** conducts the potential of one electrode of the EL element **402** retained by the Cs **503** to the signal detector circuit while suppressing deterioration (generation of noise). In view of the potential difference between the electrodes of the EL element **402**, which is detected in the signal detector circuit, the reference potential (Vcom) of the power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the Cs **503** functions as a memory element for retaining the potential difference between the electrodes of the EL element: the SW-1 Tr **501** is non-selected (turned off) after charge is accumulated in the Cs **503**, thereby retaining the charge accumulated in the Cs **503**. Therefore, even in the state where the driving transistor **401** is off and current does not flow into the EL element **402**, the potential of one electrode of the EL element which is retained by the Cs **503** can be conducted to the gate of the SW-2 Tr **502**; accordingly, the potential difference between the electrodes of the EL element **402** can be detected to compensate for reduction in luminance due to deterioration of the EL element **402** even in the state where current does not flow into the EL element.

According to this circuit, like Embodiment 1, the current which flows into the EL element or the luminance of the EL

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element is not decreased. An input load of the signal detector circuit side does not directly affect the light emission of the EL element, that is, display. As shown in FIG. 3B, as the EL element deteriorates, the voltage which is applied to the EL element is increased by $\Delta V_{EL} = V_{EL} - V_{EL}$. The signal detector circuit monitors the voltage which is applied to the EL element and V_{EL} is calculated, and the reference potential of the EL element is increased by ΔV_{com} where $\Delta V_{com} > \Delta V_{EL}$. Accordingly, the amount of current which flows into the EL element can be recovered, so that the luminance of the EL element can be returned to the luminance being before the deterioration of the EL element.

A third transistor (SW-3 Tr) **504** may be provided in the circuit shown in FIG. 7A (FIG. 7B). The SW-3 Tr **504** enables their respective electrode potentials of a plurality of EL elements to be conducted to the signal detector circuit individually as a signal current or a signal potential, so that reduction in luminance due to the deterioration of the plurality of EL elements can be compensated for each EL element.

A circuit shown in FIG. 7B includes a driving transistor **401**, an EL element **402**, a SW-1 Tr **501**, a SW-2 Tr **502**, a SW-3 Tr **504**, and a Cs **503**. Although the other of the source and the drain of the SW-2 Tr **502** is electrically connected to the signal detector circuit in FIG. 7A, the SW-3 Tr **504** is interposed between the other of the source and the drain of the SW-2 Tr **502** and a signal detector circuit in FIG. 7B. One of a source and a drain of the SW-3 Tr **504** is electrically connected to the other of the source and the drain of the SW-2 Tr **502**; and the other of the source and the drain of the SW-3 Tr **504** is electrically connected to the signal detector circuit. A gate of the SW-3 Tr **504** is electrically connected to a third signal terminal **410**.

During the period in which the driving transistor **401** is on and the EL element **402** emits light, the SW-1 Tr **501** is selected (turned on) by application of the potential of the second signal terminal **406**, thereby accumulating charge corresponding to the potential difference between the electrodes of the EL element **402** in the Cs **503** and conducting the potential of one electrode of the EL element **402** to the gate of the SW-2 Tr **502**. Then, the SW-3 Tr **504** is selected by application of the potential of the third signal terminal **410**, thereby conducting the potential of one electrode of the EL element **402** to the signal detector circuit as a signal current or a signal potential. At this time, the SW-2 Tr **502** conducts the potential of one electrode of the EL element **402** retained by the Cs **503** to the signal detector circuit while suppressing deterioration (generation of noise). Then, in view of the potential difference between the electrodes of the EL element **402**, which is detected in the signal detector circuit, the reference potential (V_{com}) of the power source terminal connected to the other electrode of the EL element is controlled, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this structure, the Cs **503** functions as a memory element for retaining the potential difference between the electrodes of the EL element: the SW-1 Tr **501** is non-selected (turned off) after charge is accumulated in the Cs **503**, thereby retaining the charge accumulated in the Cs **503**. Therefore, even in the state where the driving transistor **401** is off and current does not flow into the EL element, the potential of one electrode of the EL element which is retained by the Cs **503** can be conducted to the gate of the SW-2 Tr **502**; therefore, the potential of one electrode of the EL element which is retained by the Cs **503** can be conducted to the signal detector circuit as appropriate by turning the SW-3 Tr **504** on. Accordingly, the potential difference between the electrodes of the EL element **402** can be detected to compensate for the reduction in luminance due to

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deterioration of the EL element **402** even in the state where the driving transistor **401** is off and current does not flow into the EL element **402**.

The SW-3 Tr **504** is selected by application of the potential of the third signal terminal **410**, so that the potential of one electrode of the EL element **402** retained by the Cs **503** can be conducted to the signal detector circuit. Therefore, their respective electrode potentials of a plurality of EL elements can be conducted to the signal detector circuit individually as a signal current or a signal potential, so that reduction in luminance of the deterioration of the plurality of EL elements can be compensated for each EL element.

The operation of the circuit shown in FIG. 7B will be described using a timing chart shown in FIG. 8. The driving transistor **401** functions as a switch for conducting current to the EL element **402**. A potential V_{g1} is conducted to the first signal terminal **403**. When V_{g1} is higher than the threshold voltage of the driving transistor **401**, the driving transistor **401** is turned on, so that the potential difference between the power source potential V_{dd} and the potential of a second power source terminal which is connected to the EL element is applied to the EL element **402** as a voltage (V_{EL}). As a result, the EL element **402** emits light. On the other hand, when V_{g1} is lower than the threshold voltage of the driving transistor **401**, the driving transistor **401** is turned off not to conduct the power source potential V_{dd} to the EL element **402**, so that the EL element **402** does not emit light.

The driving transistor **401** is turned on by application of the potential V_{g1} of the first signal line to conduct the potential difference V_{EL} between the electrodes of the EL element **402**, so that the EL element **402** emits light. Next, the SW-1 Tr **501** is turned on by application of the potential of the second signal line, so that charge corresponding to the potential difference which is applied to the EL element **402** is accumulated in the Cs **503** and the potential of one electrode of the EL element **402** is applied to the gate of the SW-2 Tr **502** to turn the SW-2 Tr **502** on. After the charge is accumulated in the Cs **503**, the SW-1 Tr **501** is turned off, so that the charge accumulated in the Cs **503** is retained.

Next, the driving transistor **401** is turned off by application of the potential V_{g1} of the first signal line, so that the light emission of the EL element **402** is decayed. After that, the SW-3 Tr **504** is turned on by application of a potential V_{g3} of the third signal line, thereby conducting the potential of one electrode of the EL element **402** to the signal detector circuit as a signal current or a signal potential (V_{out}). In this structure, the Cs **503** functions as a memory element for retaining the potential difference between the electrodes of the EL element, and the potential difference between the electrodes of the EL element **402** can be conducted to the signal detector circuit by application of the potential of the third signal terminal **410** even in the period in which the EL element **402** does not emit light. As shown in FIG. 3B, as the EL element deteriorates, the voltage which is applied to the EL element is increased by $\Delta V_{EL} = V_{EL} - V_{EL}$. The signal detector circuit monitors the voltage which is applied to the EL element and V_{EL} is calculated, and the reference potential of the EL element is increased by ΔV_{com} where $\Delta V_{com} > \Delta V_{EL}$. Accordingly, the amount of current which flows into the EL element can be recovered, so that the luminance of the EL element can be returned to the luminance being before the deterioration of the EL element. In FIG. 8, the state where the voltage which is higher by ΔV_{com} is applied between the electrodes of the EL element at the timing before the EL element emits light next is shown.

The potential difference between the electrodes of the EL element before deterioration, which is a reference value for

compensation of the luminance of the EL element, can be detected at any timing as appropriate: for example, at the time when power is on, or for each period of time.

The conductivity types of the driving transistor **401**, the SW-1 Tr **501**, the SW-2 Tr **502**, and the SW-3 Tr **504** are individually either an n-type or a p-type.

According to this circuit, the luminance of the EL element can be compensated without reduction in the current flowing into the EL element or the luminance of the EL element. An input load of the signal detector circuit side does not directly affect the light emission of the EL element, that is, display. Further, by the provision of the SW-3 Tr **504**, their respective voltages which are applied to a plurality of EL elements can be detected individually, so that reduction in luminance due to deterioration of the plurality of EL elements can be compensated for each EL element.

Embodiment 3

In this embodiment, the case where the present invention is applied to an active matrix display device in which a plurality of pixels is provided and an EL element is provided for each pixel will be described.

A circuit shown in FIG. 9 includes a driving transistor **601**, an EL element **602**, a SW-1 Tr **604**, a SW-2 Tr **606**, a first storage capacitor Cs **605**, a fourth transistor (SW-4 Tr) **607**, a second storage capacitor Cs **608**, a first scanning line **610**, a second scanning line **612**, a signal line **609**, and a power source line **611**. A potential on the high-potential side of a power source (a power source potential, Vdd) is applied to the power source line **611**; and a potential on the low-potential side of the power source (a reference potential) is applied to a power source terminal **603**, in which the potential corresponds to the reference potential (Vcom) of the EL element **602**.

A gate of the SW-4 Tr **607** is electrically connected to the first scanning line **610**; one of a source and a drain thereof is electrically connected to the signal line **609**; and the other of the source and the drain thereof is electrically connected to a gate of the driving transistor **601** and one electrode of the second storage capacitor Cs **608**. One of a source and a drain of the driving transistor **601** is electrically connected to the power source line **611** and the other electrode of the second storage capacitor Cs **608**; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the SW-1 Tr **604** and one electrode of the EL element **602**. A gate of the SW-1 Tr **604** is electrically connected to the first scanning line **610**; and the other of the source and the drain of SW-1 Tr **604** is electrically connected to one electrode of the first storage capacitor Cs **605** and one of a source and a drain of the SW-2 Tr **606**. The other electrode of the first storage capacitor Cs **605** is electrically connected to the other electrode of the EL element **602** and the power source terminal **603**. A gate of the SW-2 Tr **606** is electrically connected to the second scanning line **612**; and the other of the source and the drain of the SW-2 Tr **606** is electrically connected to a signal detector circuit.

The SW-2 Tr **606** in a circuit surrounded by a dotted line conducts charge accumulated in the first storage capacitor Cs **605** to the signal detector circuit as a signal current or a signal potential. According to this, the potential difference which is applied between the electrodes of the EL element in one pixel can be detected. The reference potential of the EL element is controlled in view of the change in the detected potential difference which is applied between the electrodes of the EL element, thereby compensating the reduction in luminance due to deterioration of the EL element. The circuit surrounded

by the dotted line is not necessarily provided per pixel but may be provided per row or column of pixels.

The operation of the circuit shown in FIG. 9 will be described using a timing chart in one frame period, shown in FIG. 10. The SW-4 Tr **607** functions as a switch for conducting the potential of the signal line **609** to the driving transistor **601** and the Cs **608**. The driving transistor **601** functions as a switch for conducting current to the EL element **602**. Reference symbol Vg1 denotes the potential of the first scanning line **610**. When Vg1 is higher than the threshold voltage of the SW-4 Tr **607**, the SW-4 Tr **607** is turned on, so that the potential of the signal line **609** is conducted to the gate of the driving transistor **601** (Signal Writing). At the same as this time, the potential of the signal line **609** is also conducted to the other electrode of the second storage capacitor Cs **608**. The second storage capacitor Cs **608** retains the gate potential of the driving transistor **601**. In the case where the parasitic capacitance between the gate and the source or the gate and the drain of the driving transistor **601** is large, it is not necessary to provide the second storage capacitor Cs **608**. When Vg1 is lower than the threshold voltage of the SW-4 Tr **607**, the SW-4 Tr **607** is turned off, so that the potential of the signal line **609** (Vsig) is not conducted to the gate of the driving transistor **601**. At that time, the potential retained by the second storage capacitor Cs **608** is applied to the gate of the driving transistor **601** (Signal Retaining).

In the case where the potential of the signal line **609** is higher than the threshold voltage of the driving transistor **601**, the driving transistor **601** is turned on to conduct the potential of the power source line **611** to one electrode of the EL element **602**. As a result, the EL element **602** emits light. On the other hand, in the case where the potential of the signal line **609** is lower than the threshold voltage of the driving transistor **601**, the driving transistor **601** is turned off, so that the potential of the power source line **611** is not applied to the EL element **602** and the EL element **602** does not emit light.

The SW-1 Tr **604** and the SW-4 Tr **607** are operated in synchronization with each other and the conductivity types thereof are the same as each other (n-type or p-type). Therefore, the SW-1 Tr **604** is turned on at the time when the SW-4 Tr **607** is turned on, so that charge corresponding to the potential difference applied to the EL element **602** at that time is accumulated in the first storage capacitor Cs **605**.

In the holding period, the SW-4 Tr **607** and the SW-1 Tr **604** are turned off by application of the potential of the first scanning line **610**. At that time, when the SW-2 Tr **606**, which is connected to the first storage capacitor Cs **605**, in the circuit surrounded by the dotted line is off, the charge accumulated in the first storage capacitor Cs **605** is retained. That is, the potential which is applied to the EL element **602** in the previous signal-writing period is retained in the first storage capacitor Cs **605**. Then, the SW-2 Tr **606** is turned on in the retaining period, so that the charge accumulated in the first storage capacitor Cs **605** can be conducted to the signal detector circuit as a signal current or a signal current. As shown in FIG. 3B, as the EL element deteriorates, the voltage which is applied to the EL element is increased by $\Delta V_{EL} = V_{EL} - V_{EL'}$. The signal detector circuit monitors the voltage which is applied to the EL element and calculates ΔV_{EL} , and the reference potential of the EL element is increased by ΔV_{com} where $\Delta V_{com} > \Delta V_{EL}$. Accordingly, the amount of current which flows into the EL element can be recovered, so that the luminance of the EL element can be returned to the luminance being before the deterioration of the EL element. In FIG. 10, the state where the voltage which is higher by ΔV_{com} is applied between the electrodes of the EL element at the timing before the EL element emits light next is shown.

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ON/OFF of the SW-2 Tr 606 can be changed by changing the potential Vg2 of the second scanning terminal 612: when Vg2 is higher than the threshold voltage of the SW-2 Tr 606, the SW-2 Tr 606 is turned on whereas when Vg2 is lower than the threshold voltage of the SW-2 Tr 606, the SW-2 Tr 606 is turned off. This circuit configuration enables the voltage which is applied to the EL element 602 to be detected in the retaining period; accordingly, the luminance of the EL element 602 can be compensated without reduction in the current which flows into the EL element 602 or reduction in the luminance of the EL element 602. An input load of the signal detector circuit side does not directly affect the light emission of the EL element, that is, display.

Although the gate of the SW-1 Tr 604 and the gate of the SW-4 Tr 607 are connected to and controlled by the first scanning line in FIG. 10, they may be controlled by different scanning lines (FIG. 11).

In a circuit shown in FIG. 11, a gate of a SW-1 Tr 604 is electrically connected to and controlled by a third scanning line 613, and a gate of a SW-4 Tr 607 is electrically connected to and controlled by a first scanning line 610. Accordingly, the period in which the SW-1 Tr 604 is on can be set as appropriate in the period in which an EL element 602 emits light. Further, the conductivity types of the SW-1 Tr 604 and the SW-4 Tr 607 may be different from each other.

The potential difference between the electrodes of the EL element before deterioration, which is a reference value for compensation of luminance of the EL element, can be detected at any timing as appropriate: for example, at the time when power is on, or for each period of time.

Embodiment 4

In the circuit according to Embodiment 3, the charge accumulated in the first storage capacitor is conducted to the signal detector circuit as a signal current or a signal potential through the second transistor. The potential retained in the first storage capacitor may be conducted to the signal detector circuit through a third transistor (FIG. 12).

A circuit shown in FIG. 12 includes a driving transistor 601, an EL element 602, a SW-1 Tr 604, a SW-2 Tr 606, a SW-3 Tr 614, a first storage capacitor Cs 605, a SW-4 Tr 607, a second storage capacitor Cs 608, a first scanning line 610, a second scanning line 612, a signal line 609, and a power source line 611. A potential on the high-potential side of a power source (a power source potential, Vdd) is applied to the power source line 611; and a potential on the low-potential side of the power source (a reference potential) is applied to a power source terminal 603, in which the potential corresponds to the reference potential (Vcom) of the EL element 602.

A gate of the SW-4 Tr 607 is electrically connected to the first scanning line 610; one of a source and a drain thereof is electrically connected to the signal line 609; and the other of the source and the drain thereof is electrically connected to a gate of the driving transistor 601 and one electrode of the second storage capacitor Cs 608. One of a source and a drain of the driving transistor 601 is electrically connected to the power source line 611 and the other electrode of the second storage capacitor Cs 608; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the SW-1 Tr 604 and one electrode of the EL element 602. A gate of the SW-1 Tr 604 is electrically connected to the first scanning line 610; and the other of the source and the drain of SW-1 Tr 604 is electrically connected to one electrode of the first storage capacitor Cs 605 and a gate of the SW-3 Tr 614. The other electrode of the first storage

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capacitor Cs 605 is electrically connected to the other electrode of the EL element 602 and the power source terminal 603. One of a source and a drain of the SW-3 Tr 614 is electrically connected to the power source line 611; and the other of the source and the drain thereof is electrically connected to one of a source and a drain of the SW-2 Tr 606. A gate of the SW-2 Tr 606 is electrically connected to the second scanning line 612; and the other of the source and the drain thereof is electrically connected to a signal detector circuit.

In the circuit shown in FIG. 12, the SW-3 Tr 614 which conducts the potential of one electrode of the first storage capacitor Cs 605 or the potential of one electrode of the EL element 602 while suppressing deterioration (generation of noise) is provided. When the SW-1 Tr 604 is on, charge corresponding to the potential difference of the EL element 602 is accumulated in the first storage capacitor Cs 605. In addition, the potential of one electrode of the EL element 602 is also conducted to the gate of the SW-3 Tr 614. Next, the SW-1 Tr 604 is turned off by application of the potential of the first scanning line 610, that is, the retaining period is started, so that the charge accumulated in the first storage capacitor Cs 605 can be retained.

Next, the SW-2 Tr 606 is turned on, so that the potential of one electrode of the first storage capacitor Cs 605 can be conducted to the signal detector circuit in the retaining period. Accordingly, the reference potential (Vcom) of the power source terminal 603 connected to the EL element 602 can be controlled in view of the change in the detected potential difference of the EL element 602, so that the reduction in luminance due to deterioration of the EL element can be compensated without reduction in the current which flows into the EL element or reduction in the luminance of the EL element. An input load of the signal detector circuit side does not directly affect the light emission of the EL element, that is, display.

Note that a circuit which has a similar function to or the same function as the SW-3 Tr 614 may be provided on the signal detection circuit side in common with pixels; however, as compared with that case, the noise of signals can be reduced by amplifying each signal for each pixel before conducting to the signal detector circuit.

The conductivity type of the SW-3 Tr 614 is n-type when the potential of the power source line 611 is positive, and is p-type when the potential of the power source line 611 is negative. In this manner, the SW-3 Tr 614 can be used as a source follower for amplification.

Although the gate of the SW-1 Tr 604 and the gate of the SW-4 Tr 607 are electrically connected to and controlled by the first scanning line in the circuit shown in FIG. 12, they may be controlled by different scanning lines (FIG. 13).

In a circuit shown in FIG. 13, a gate of a SW-1 Tr 604 is electrically connected to and controlled by a third scanning line 613, and a gate of a SW-4 Tr 607 is electrically connected to and controlled by a first scanning line 610. Accordingly, the period in which the SW-1 Tr 604 is on can be set as appropriate in the period in which an EL element 602 emits light. Further, the conductivity types of the SW-1 Tr 604 and the SW-4 Tr 607 may be different from each other.

The potential difference between the electrodes of the EL element before deterioration, which is a reference value for compensation of the luminance of the EL element, can be detected at any timing as appropriate: for example, at the time when power is on, or for each period of time.

Embodiment 5

An active matrix circuit using the circuit shown in FIG. 9 is shown in FIG. 14. The active matrix circuit shown in FIG. 14

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includes a first scanning line driver circuit **652** for selecting the switching transistor (SW-4 Tr) **607**, a signal line driver circuit **651** for controlling the potential of the signal line **609**, a second scanning line driver circuit **653** for selecting the SW-2 Tr **606**, a power source circuit **650**, and a signal detector circuit **654**. The signal detector circuit **654** controls the potential of a second power source line **655** connected to the EL element **602** in view of the change in the detected potential difference of the EL element, thereby compensating for the reduction in luminance due to deterioration of the EL element. In this circuit, the second power source terminals of a plurality of EL elements are connected to the second power source line **655** as a common line. Therefore, FIG. **14** illustrates an example of a circuit in which the potential of the power source line can be changed for each row. A portion surrounded by a dotted line corresponds to one pixel.

The circuit shown in FIG. **9** is incorporated in each of a plurality of pixels, the potential difference of the EL element **602** is detected from each pixel as appropriate, and the potential of the second power source line **655**, that is, the reference potential (Vcom) of the EL element **602** is controlled. Note that the provision of power source lines **611** is not limited to that shown in FIG. **14**: the power source lines **611** may be each provided per row or a plurality of power source lines may be provided in common with each other. By providing a plurality of circuits each for detecting the potential difference of an EL element such as the circuits shown in FIG. **9**, **10**, **11**, **12**, or **13**, in a matrix, distribution of the potential difference of a plurality of EL elements can be detected. Their respective reference potentials of the plurality of EL elements are controlled in view of the potential difference, thereby compensating for the variation of the luminance within a panel.

The circuit for detecting the potential difference of an EL element such as the circuit shown in FIG. **9**, **10**, **11**, **12**, or **13** may be provided for every pixel.

When the reference potential of the EL element is compensated based on the detected potential difference, the compensation value may be determined in accordance with the value of the worst-deteriorated EL element. Alternatively, compensation values of a plurality of EL elements may be averaged, and the reference potential of each EL element may be compensated based on the average value. In the case where compensation is performed in accordance with the compensation value of the worst-deteriorated EL element, driving of the EL elements of all the pixels can be surely returned to driving in the saturation region whereas rise in the power consumption is increased. On the other hand, in the case where the compensation values of all the pixels are determined in accordance with the average value of their respective compensation values of a plurality of EL elements, driving of the EL elements of all the pixels cannot be returned to driving in the saturation region whereas rise in the power consumption can be suppressed. The compensation value of the reference potential can be determined in accordance with the standard needed for panel display.

With the use of the circuit for compensating the driving voltage of an EL element, according to the present invention, the driving operation point shifted due to deterioration of the EL element can be returned to an operation point being before the deterioration, thereby compensating for the reduction in luminance due to the deterioration of an EL element. Furthermore, an operation point of the EL element in the saturation region can be set near the linear region as much as possible. In this manner, the source-drain voltage which is applied to a driving transistor is decreased, so that the reliability of the driving transistor can be improved. In addition, the luminance of the EL element can be retained.

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The present invention is different from the case where a pixel for monitoring an EL element is provided in or around a display pixel; therefore, it is not necessary to provide a pixel which does not contribute toward displaying. Further, since compensation is not performed based on a pixel which does not contribute toward displaying but is performed based on a pixel which contributes toward displaying, luminance compensation of EL elements can be performed with high accuracy.

Embodiment 6

A cross-sectional view of a light-emitting device of the present invention is shown in FIG. **15**, in which typically, a first transistor **700**, a storage capacitor **701**, and an EL element **702** are shown.

Although a top-gate thin film transistor is shown in FIG. **15**, either a bottom-gate thin film transistor (TFT) or a top-gate thin film transistor (TFT) can be used as each of a driving transistor, a first transistor, a second transistor, a third transistor, and a fourth transistor.

A semiconductor layer **703** of the TFT can be formed using an inorganic semiconductor such as: a semiconductor such as Si, a compound semiconductor such as SiGe or GaAs, or an oxide semiconductor such as ZnO. The inorganic semiconductor may be any of amorphous, microcrystalline, or single-crystalline. Alternatively, an organic semiconductor such as pentacene or oligothiophene can be used. The semiconductor layer **703** is formed by a CVD method, a sputtering method, or the like. Further, in the case where an amorphous semiconductor film is crystallized, a laser crystallization method, a heat crystallization method, or the like can be used.

The TFT is either an n-channel TFT or a p-channel TFT. An impurity region **704** is either an n-type impurity region or a p-type impurity region. Addition of the impurity thereof can be performed by an ion-doping method or the like.

A gate insulating film **705** can be formed using an insulating film such as a silicon oxide film (SiO₂), a silicon oxynitride film (SiON), a silicon nitride oxide film (SiNO), a silicon nitride film (SiN), an aluminum oxide film (Al₂O₃), or a barium titanate film (BaTiO₃). A high-dielectric-constant insulating film such as a hafnium silicon oxynitride film (Hf-SiON) or an yttrium oxide film (Y₂O₃) may be used as well. The gate insulating film **705** can be formed by a thermal oxidation method, a plasma oxidation method, a CVD method, or a sputtering method.

A gate electrode **706**, an electrode such as a source electrode **707** or a drain electrode **707**, and a wiring such as a scanning line and a signal line can be formed using a single-layer film of tungsten, aluminum, titanium, or tantalum, or a stack-layer film thereof. Each electrode and each wiring can be formed as follows: a metal film is formed by a sputtering method and processed by an etching method. Alternatively, a metal nano paste of silver, gold, or the like can be formed by a droplet-discharge method.

The storage capacitor **701** can be formed including one electrode **708** which is a semiconductor layer in which an n-type or p-type impurity which is the same as the impurity type as the TFT is added, the other electrode **709** which is formed of the same layer as the gate electrode, and the gate insulating film **705**. The other electrode **709** of the storage capacitor **701** is electrically connected to the other electrode **713** of the EL element (not shown).

As an insulating film **710** for covering the TFT and the storage capacitor, an inorganic insulating film such as a silicon oxide film or a silicon nitride film or an organic insulating film of an acrylic resin can be used. The inorganic insulating

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film can be formed by a CVD method or a sputtering method, and the organic insulating film can be formed by a spin-coating method.

The EL element **702** includes one electrode **711**, a light-emitting layer **712**, and the other electrode **713**. Either an organic EL element or an inorganic EL element can be used.

In the case of an organic EL element, a fluorescence emission material or a phosphorescence emission material can be used. As the light emission material, either a low-polymer material or a high-polymer material can be used.

As the light-emitting layer **712**, a hole-injecting layer, a hole-transporting layer, an electron-transporting layer, and/or an electron-injecting layer are/is provided as appropriate. A light emission material may be doped into a host material.

In the case of an inorganic EL element, a semiconductor such as ZnO, $\text{Mg}_x\text{Zn}_{1-x}\text{O}$, ZnS, ZnTe, or CdS can be used.

The light-emitting layer is formed by a vapor deposition method, a spin-coating method, a droplet-discharge method, or the like.

As each of the electrodes **711** and **713**, a metal film or a transparent conductive film of Al, Ti, Mo, Ag, Pt, W, indium tin oxide (ITO), or the like can be used. In that case, a single-layer film or a stack-layer film thereof can be used. A sputtering method, a vapor deposition method, or the like is used.

A bank **714** may be formed using an insulating film.

As a substrate **715**, glass, plastics, paper, or the like can be used.

Embodiment 7

There are various applications of the light-emitting device of the present invention. In this embodiment, examples of an electronic device to which the present invention can be applied will be described.

As such an electronic device, a personal digital assistance (such as an electronic notebook, a mobile computer, and a mobile phone), a video camera, a digital camera, a personal computer, a television, and the like can be given. Examples of these are illustrated in FIGS. **16A** to **16F**.

FIG. **16A** illustrates an EL display, which includes a housing **3301**, a support **3302**, a display portion **3303**, and the like. The light-emitting device of the present invention can be used in the display portion **3303**.

FIG. **16B** illustrates a video camera, which includes a main body **3311**, a display portion **3312**, a sound input portion **3313**, operation switches **3314**, a battery **3315**, an image receiving portion **3316**, and the like. The light-emitting device of the present invention can be used in the display portion **3312**.

FIG. **16C** illustrates a personal computer, which includes a main body **3321**, a housing **3322**, a display portion **3323**, a keyboard **3324**, and the like. The light-emitting device of the present invention can be used in the display portion **3323**.

FIG. **16D** illustrates a personal digital assistance, which includes a main body **3331**, a stylus **3332**, a display portion **3333**, operation buttons **3334**, an outside interface **3335**, and the like. The light-emitting device of the present invention can be used in the display portion **3333**.

FIG. **16E** illustrates a mobile phone, which includes a main body **3401**, a sound output portion **3402**, a sound input portion **3403**, a display portion **3404**, operation switches **3405**, an antenna **3406**, and the like. The light-emitting device of the present invention can be used in the display portion **3404**.

FIG. **16F** illustrates a digital camera, which includes a main body **3501**, a display portion (A) **3502**, an eyepiece **3503**, operation switches **3504**, a display portion (B) **3505**,

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and a battery **3506**. The light-emitting device of the present invention can be used in the display portion (A) **3502** and the display portion (B) **3505**.

FIG. **17** illustrates an example in which a light-emitting device to which the present invention is applied is used as an indoor lighting system **3001**. Since the area of the light-emitting device of the present invention can be increased, the light-emitting device of the present invention can be used as a lighting system having a large emission area. Thus, a television device **3002** according to the present invention may be placed in a room where the light-emitting device to which the present invention is applied is used as the indoor lighting system **3001** so that public broadcasting or movies can be enjoyed.

As described above, the application range of the present invention is very wide; and the present invention can be used for electronic devices in various fields.

This application is based on Japanese Patent Application serial no. 2008-184970 filed with Japan Patent Office on Jul. 16, 2008, the entire contents of which are hereby incorporated by reference.

What is claimed is:

1. A light-emitting device comprising:

a driving transistor;

an electroluminescence element;

a first transistor;

a first power source;

a second power source;

a first signal terminal;

a second signal terminal; and

a signal detector circuit,

wherein a gate of the driving transistor is electrically connected to the first signal terminal, one of a source and a drain of the driving transistor is electrically connected to the first power source, and the other of the source and the drain of the driving transistor is electrically connected to one of a source and a drain of the first transistor and one electrode of the electroluminescence element,

wherein a gate of the first transistor is electrically connected to the second signal terminal, and the other of the source and the drain of the first transistor is electrically connected to the signal detector circuit, and

wherein the other electrode of the electroluminescence element is electrically connected to the second power source.

2. An electronic appliance having the light-emitting device according to claim **1**, wherein the electronic appliance is one selected from an electronic notebook, a mobile computer, a mobile phone, a video camera, a digital camera, a television, and the like.

3. A light-emitting device comprising:

a driving transistor;

a first transistor;

a second transistor;

an electroluminescence element;

a storage capacitor;

a first signal terminal;

a second signal terminal;

a first power source;

a second power source;

a third signal terminal; and

a signal detector circuit,

wherein a gate of the driving transistor is electrically connected to the first signal terminal, one of a source and a drain of the driving transistor is electrically connected to the first power source, and the other of the source and the drain of the driving transistor is electrically connected to

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one of a source and a drain of the first transistor and one electrode of the electroluminescence element, wherein a gate of the first transistor is electrically connected to the second signal terminal, and the other of the source and the drain of the first transistor is electrically connected to one electrode of the storage capacitor and one of a source and a drain of the second transistor, wherein the other electrode of the storage capacitor is electrically connected to the other electrode of the electroluminescence element and the second power source, and

wherein a gate of the second transistor is electrically connected to the third signal terminal, and the other of the source and the drain of the second transistor is electrically connected to the signal detector circuit.

4. The light-emitting device according to claim 3, wherein the storage capacitor is a capacitor for accumulating a charge corresponding to a potential difference between electrodes of the electroluminescence element.

5. The light-emitting device according to claim 3, wherein the storage capacitor retains charge corresponding to a potential difference between electrodes of the electroluminescence element.

6. An electronic appliance having the light-emitting device according to claim 3, wherein the electronic appliance is one selected from an electronic notebook, a mobile computer, a mobile phone, a video camera, a digital camera, a television, and the like.

7. A light-emitting device comprising:

a driving transistor;
a first transistor;
a second transistor;
a storage capacitor;
an electroluminescence element;
a first signal terminal;
a second signal terminal;
a first power source;
a second power source; and
a signal detector circuit,

wherein a gate of the driving transistor is electrically connected to the first signal terminal, one of a source and a drain of the driving transistor is electrically connected to the first power source, and the other of the source and the drain of the driving transistor is electrically connected to one of a source and a drain of the first transistor and one electrode of the electroluminescence element,

wherein a gate of the first transistor is electrically connected to the second signal terminal, and the other of the source and the drain of the first transistor is electrically connected to one electrode of the storage capacitor and a gate of the second transistor,

wherein the other electrode of the storage capacitor is electrically connected to the other electrode of the electroluminescence element and the second power source, and

wherein one of a source and a drain of the second transistor is electrically connected to the first power source, and the other of the source and the drain of the second transistor is electrically connected to the signal detector circuit.

8. The light-emitting device according to claim 7, wherein the storage capacitor is a capacitor for accumulating a charge corresponding to a potential difference between electrodes of the electroluminescence element.

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9. The light-emitting device according to claim 7, wherein the storage capacitor retains charge corresponding to a potential difference between electrodes of the electroluminescence element.

10. An electronic appliance having the light-emitting device according to claim 7, wherein the electronic appliance is one selected from an electronic notebook, a mobile computer, a mobile phone, a video camera, a digital camera, a television, and the like.

11. A light-emitting device comprising:

a driving transistor;
a first transistor;
a second transistor;
a third transistor;
an electroluminescence element;
a storage capacitor;
a first signal terminal;
a second signal terminal;
a third signal terminal;
a first power source;
a second power source; and
a signal detector circuit,

wherein a gate of the driving transistor is electrically connected to the first signal terminal, one of a source and a drain of the driving transistor is electrically connected to the first power source, and the other of the source and the drain of the driving transistor is electrically connected to one of a source and a drain of the first transistor and one electrode of the electroluminescence element,

wherein a gate of the first transistor is electrically connected to the second signal terminal, and the other of the source and the drain of the first transistor is electrically connected to one electrode of the storage capacitor and a gate of the second transistor,

wherein the other electrode of the storage capacitor is electrically connected to the other electrode of the electroluminescence element and the second power source, wherein one of a source and a drain of the second transistor is electrically connected to the first power source, and the other of the source and the drain of the second transistor is electrically connected to one of a source and a drain of the third transistor, and

wherein a gate of the third transistor is electrically connected to the third signal terminal, and the other of the source and the drain of the third transistor is electrically connected to the signal detector circuit.

12. The light-emitting device according to claim 11, wherein the storage capacitor is a capacitor for accumulating a charge corresponding to a potential difference between electrodes of the electroluminescence element.

13. The light-emitting device according to claim 11, wherein the storage capacitor retains charge corresponding to a potential difference between electrodes of the electroluminescence element.

14. An electronic appliance having the light-emitting device according to claim 11, wherein the electronic appliance is one selected from an electronic notebook, a mobile computer, a mobile phone, a video camera, a digital camera, a television, and the like.

15. A light-emitting device comprising:

a driving transistor;
a switching transistor;
a first transistor;
a second transistor;
an electroluminescence element;
a first storage capacitor;
a second storage capacitor;

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a first scanning line;
a second scanning line;
a signal line;
a power source line;
a power source; and
a signal detector circuit,

wherein a gate of the switching transistor is electrically connected to the first scanning line, one of a source and a drain of the switching transistor is electrically connected to the signal line, and the other of the source and the drain of the switching transistor is electrically connected to a gate of the driving transistor and one electrode of the second storage capacitor,

wherein one of a source and a drain of the driving transistor is electrically connected to the power source line and the other electrode of the second storage capacitor, and the other of the source and the drain of the driving transistor is electrically connected to one of a source and a drain of the first transistor and one electrode of the electroluminescence element,

wherein the other of the source and the drain of the first transistor is electrically connected to one electrode of the first storage capacitor and one of a source and a drain of the second transistor,

wherein the other electrode of the first storage capacitor is electrically connected to the other electrode of the electroluminescence element and the power source, and

wherein a gate of the second transistor is electrically connected to the second scanning line, and the other of the source and the drain of the second transistor is electrically connected to the signal detector circuit.

16. The light-emitting device according to claim 15, wherein the light-emitting device is an active matrix type and the second transistor and the second scanning line are provided per column or row of pixels.

17. The light-emitting device according to claim 15, wherein the second transistor is a source follower transistor for amplifying a potential difference between electrodes of the electroluminescence element.

18. The light-emitting device according to claim 15, wherein the first storage capacitor is a capacitor for accumulating a charge corresponding to a potential difference between electrodes of the electroluminescence element.

19. The light-emitting device according to claim 15, wherein a gate of the first transistor is electrically connected to the first scanning line.

20. The light-emitting device according to claim 15, wherein the driving transistor is a p-channel transistor when a potential of the power source line is positive.

21. The light-emitting device according to claim 15, wherein the driving transistor is an n-channel transistor when a potential of the power source line is negative.

22. The light-emitting device according to claim 15, wherein conductivity types of the switching transistor and the first transistor are the same.

23. An electronic appliance having the light-emitting device according to claim 15, wherein the electronic appliance is one selected from an electronic notebook, a mobile computer, a mobile phone, a video camera, a digital camera, a television, and the like.

24. A light-emitting device comprising:

a driving transistor;
a first transistor;
a second transistor;
a third transistor;
a switching transistor;
an electroluminescence element;

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a first storage capacitor;
a second storage capacitor;
a first scanning line;
a second scanning line;
a signal line;
a power source line;
a power source; and
a signal detector circuit,

wherein a gate of the switching transistor is electrically connected to the first scanning line, one of a source and a drain of the switching transistor is electrically connected to the signal line, and the other of the source and the drain of the switching transistor is electrically connected to a gate of the driving transistor and one electrode of the second storage capacitor,

wherein one of a source and a drain of the driving transistor is electrically connected to the power source line and the other electrode of the second storage capacitor, and the other of the source and the drain of the driving transistor is electrically connected to one of a source and a drain of the first transistor and one electrode of the electroluminescence element,

wherein the other of the source and the drain of the first transistor is electrically connected to one electrode of the first storage capacitor and a gate of the third transistor,

wherein the other electrode of the first storage capacitor is electrically connected to the other electrode of the electroluminescence element and the power source,

wherein one of a source and a drain of the third transistor is electrically connected to the power source line, and the other of the source and the drain of the third transistor is electrically connected to one of a source and a drain of the second transistor, and

wherein a gate of the second transistor is electrically connected to the second scanning line, and the other of the source and the drain of the second transistor is electrically connected to the signal detector circuit.

25. The light-emitting device according to claim 24, wherein the light-emitting device is an active matrix type and the second transistor and the second scanning line are provided per column or row of pixels.

26. The light-emitting device according to claim 24, wherein the second transistor is a source follower transistor for amplifying a potential difference between electrodes of the electroluminescence element.

27. The light-emitting device according to claim 24, wherein the first storage capacitor is a capacitor for accumulating a charge corresponding to a potential difference between electrodes of the electroluminescence element.

28. The light-emitting device according to claim 24, wherein a gate of the first transistor is electrically connected to the first scanning line.

29. The light-emitting device according to claim 24, wherein the driving transistor is a p-channel transistor when a potential of the power source line is positive.

30. The light-emitting device according to claim 24, wherein the driving transistor is an n-channel transistor when a potential of the power source line is negative.

31. The light-emitting device according to claim 24, wherein conductivity types of the switching transistor and the first transistor are the same.

32. An electronic appliance having the light-emitting device according to claim 24, wherein the electronic appliance

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ance is one selected from an electronic notebook, a mobile computer, a mobile phone, a video camera, a digital camera, a television, and the like.

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